

CORNERSTONE STANDARD COMPONENTS LIBRARY

(On SOI Platforms)



Preface

In this document, we summarise the up-to-date designs and their measurement results of our CORNERSTONE standard components on SOI platforms, at the same time we are optimising the current designs, adding in new designs, and gathering more measurement results. Most of the dimensions are given in this document, whilst a few of them are not. Thus, please use this document together with our up-to-date GDS library which can be downloaded at <https://www.cornerstone.sotonfab.co.uk/mpw-design-rules/process-design-kit-pdk>.

CORNERSTONE provides an MPW service on three SOI platforms, 220 nm, 340 nm and 500 nm, based on which we provide our standard components. On the 220 nm and 340 nm platforms, we have two waveguide etching depths in addition to a grating etch and we provide standard components working at 1550 nm and 1310 nm. On the 500 nm platform, we have only one waveguide etching depth in addition to a grating etch and we provide standard components working at 1550 nm only. Currently, all of the components are based on TE mode.

List of Contents

➤ **SOI220nm 1550nm**

- [SOI220nm 1550nm TE RIB Grating Coupler](#)
- [**SOI220nm 1550nm TE RIB**](#)
- [SOI220nm 1550nm TE RIB 2x1 MMI](#)
- [SOI220nm 1550nm TE RIB 2x2 MMI](#)
- [SOI220nm 1550nm TE RIB 90 Degree Bend](#)
- [SOI220nm 1550nm TE RIB Waveguide Crossing](#)
- [SOI220nm 1550nm TE RIB MM to SM TAPER](#)
- [**SOI220nm 1550nm TE STRIP**](#)
- [SOI220nm 1550nm TE STRIP 2x1 MMI](#)
- [SOI220nm 1550nm TE STRIP 2x2 MMI](#)
- [SOI220nm 1550nm TE STRIP 2x1 Ysplitter](#)
- [SOI220nm 1550nm TE Strip 90 Degree Bend](#)
- [SOI220nm 1550nm TE STRIP Waveguide Crossing](#)
- [SOI220nm 1550nm TE STRIP MM to SM TAPER](#)
- [SOI220nm 1550nm TE STRIP RIB to STRIP TAPER](#)
- [SOI220nm 1550nm TM RIB Grating Coupler](#)

➤ **SOI220nm 1310nm**

- [SOI220nm 1310nm TE RIB Grating Coupler](#)
- [**SOI220nm 1310nm TE RIB**](#)
- [SOI220nm 1310nm TE RIB 2x1 MMI](#)
- [SOI220nm 1310nm TE RIB 2x2 MMI](#)
- [SOI220nm 1310nm TE RIB Waveguide Crossing](#)
- [**SOI220nm 1310nm TE STRIP**](#)
- [SOI220nm 1310nm TE STRIP 2x1 MMI](#)
- [SOI220nm 1310nm TE STRIP 2x2 MMI](#)
- [SOI220nm 1310nm TE STRIP 2x1 Ysplitter](#)
- [SOI220nm 1310nm TE Strip 90 Degree Bend](#)
- [SOI220nm 1310nm TE STRIP Waveguide Crossing](#)
- [SOI220nm 1310nm TM RIB Grating Coupler](#)

➤ **SOI340nm 1550nm**

- [SOI340nm 1550nm TE RIB Grating Coupler](#)
- [**SOI340nm 1550nm TE RIB**](#)
- [SOI340nm 1550nm TE RIB 2x1 MMI](#)
- [SOI340nm 1550nm TE RIB 2x2 MMI](#)
- [**SOI340nm 1550nm TE STRIP**](#)
- [SOI340nm 1550nm TE STRIP 2x1 MMI](#)
- [SOI340nm 1550nm TE STRIP 2x2 MMI](#)

List of Contents

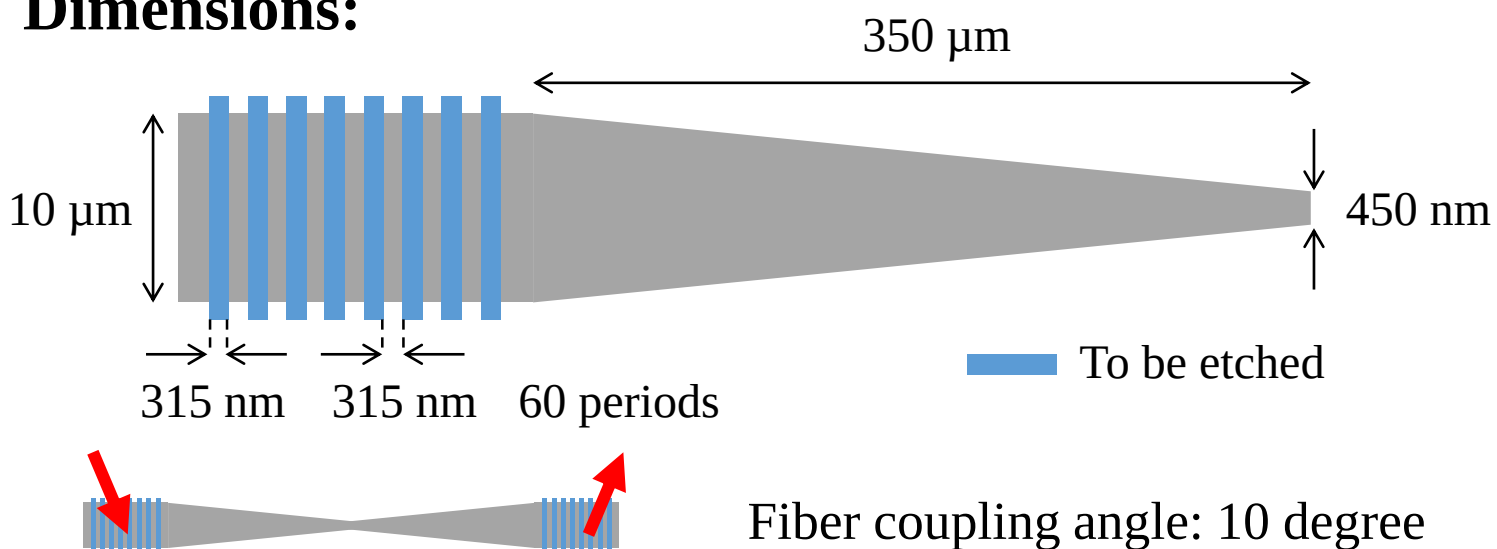
- [SOI340nm 1550nm TM RIB Grating Coupler](#)
- [**SOI340nm 1310nm**](#)
- [SOI340nm 1310nm TE RIB Grating Coupler](#)
- [**SOI340nm 1310nm TE RIB**](#)
- [SOI340nm 1310nm TE RIB 2x1 MMI](#)
- [SOI340nm 1310nm TE RIB 2x2 MMI](#)
- [**SOI340nm 1310nm TE STRIP**](#)
- [SOI340nm 1310nm TE STRIP 2x1 MMI](#)
- [SOI340nm 1310nm TE STRIP 2x2 MMI](#)
- [SOI340nm 1310nm TM RIB Grating Coupler](#)
- [**SOI500nm 1550nm**](#)
- [SOI500nm 1550nm TE RIB Grating Coupler](#)
- [**SOI500nm 1550nm TE RIB**](#)
- [SOI500nm 1550nm TE RIB 2x1 MMI](#)
- [SOI500nm 1550nm TE RIB 2x2 MMI](#)
- [SOI500nm 1550nm TE RIB 90 Degree Bend](#)
- [SOI500nm 1550nm TE RIB Waveguide Crossing Curved Design](#)
- [SOI500nm 1550nm TM RIB Grating Coupler](#)

- **Wavelength: 1550 nm**
- **Platform: 220 nm SOI**

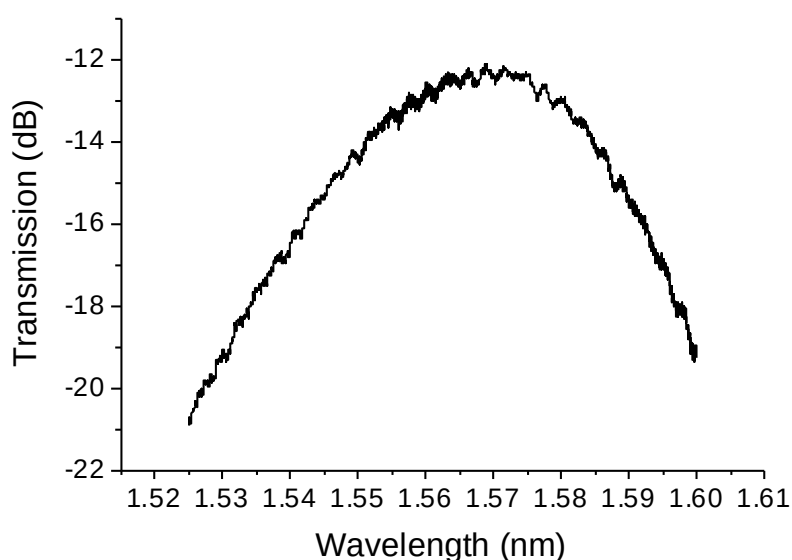
SOI220nm_1550nm_TE_RIB_Grating_Coupler

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	70 nm (Grating etch depth)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1550nm_TE_RIB_Grating_Coupler

Dimensions:



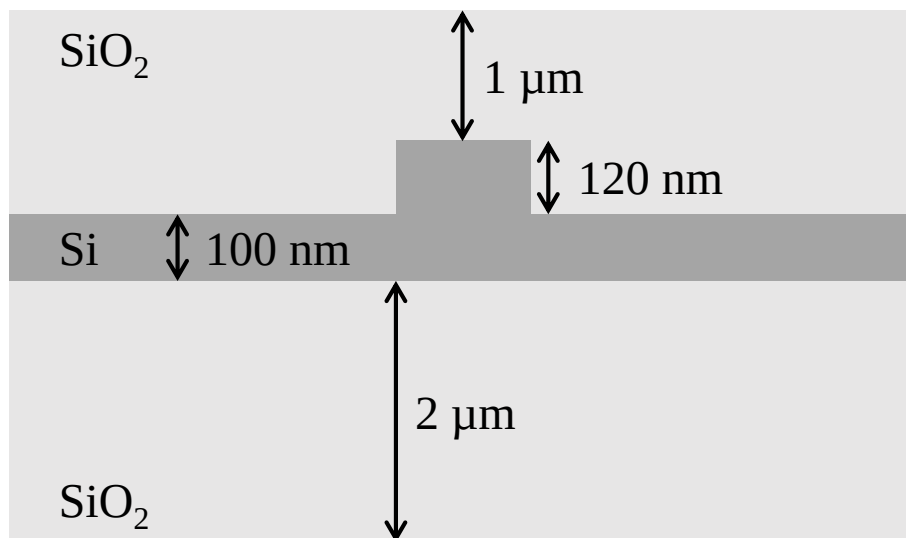
Measured transmission spectrum



Summarized performance:

- Coupling efficiency: 5.5-6.5 dB
- 1 dB bandwidth: > 35 nm
- Center wavelength: 1550-1580 nm

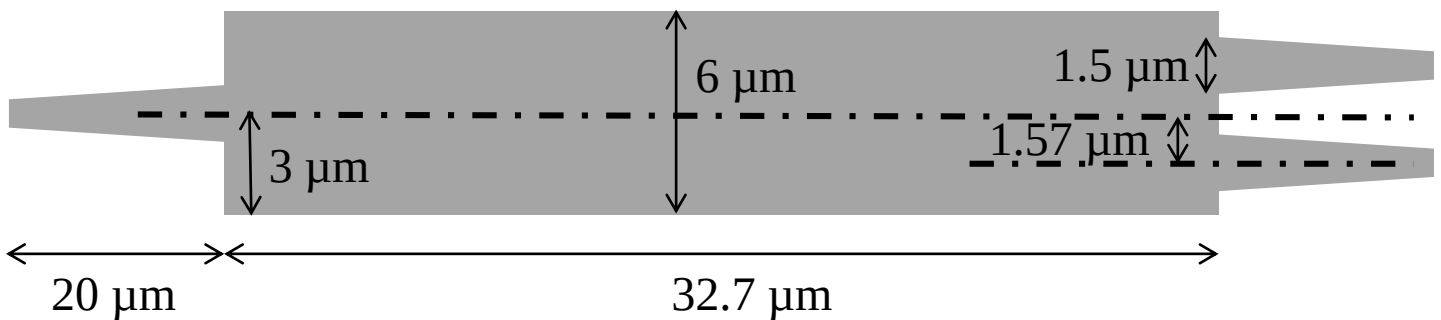
- Wavelength: 1550 nm
- Platform: 220 nm SOI
- **RIB**



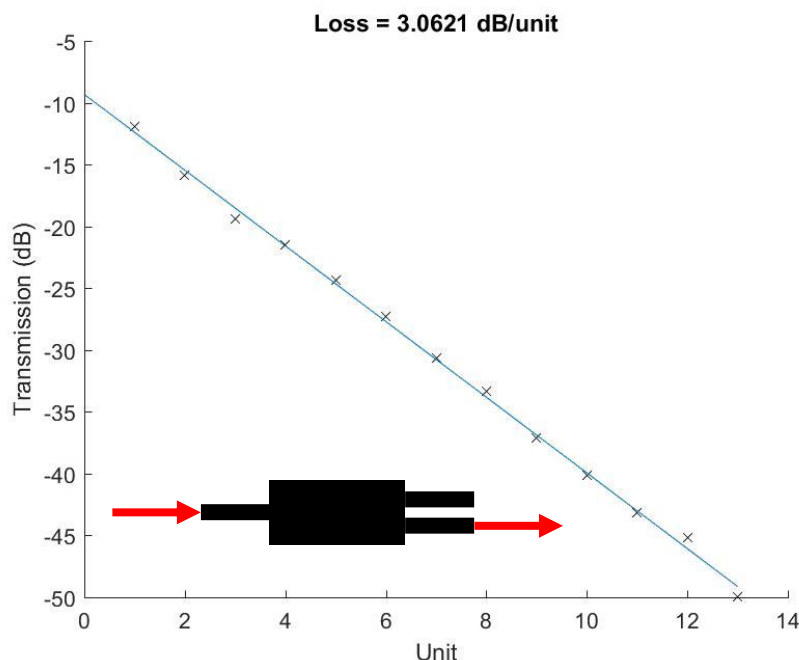
SOI220nm_1550nm_TE_RIB_2x1_MMI

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	120 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1550nm_TE_RIB_2x1_MMI

Dimensions:



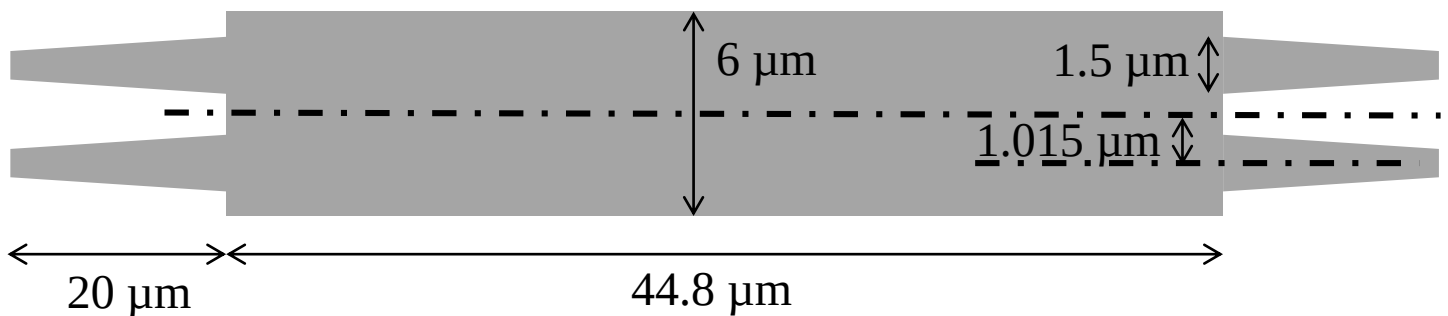
Measurement results:



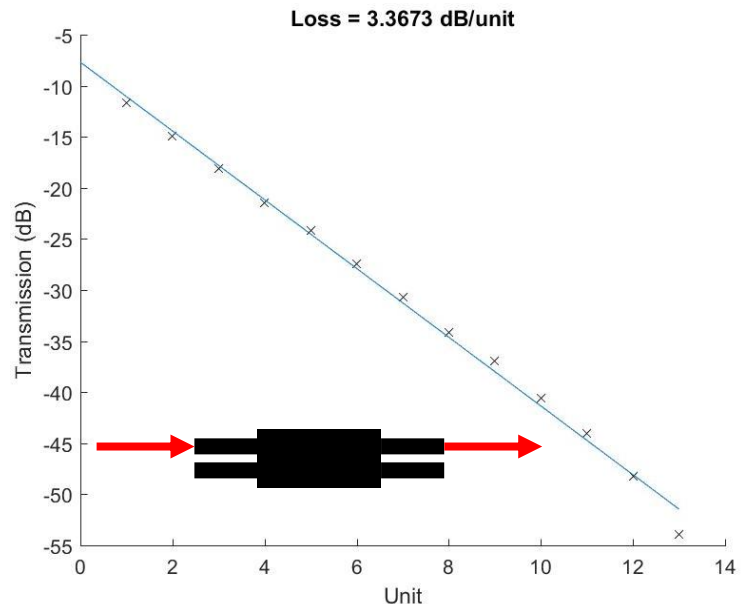
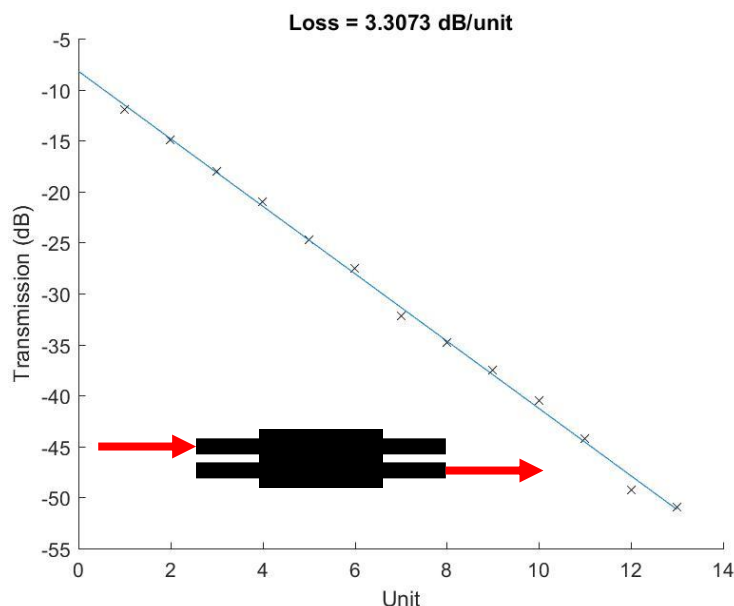
SOI220nm_1550nm_TE_RIB_2x2_MMI

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	120 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1550nm_TE_RIB_2x2_MMI

Dimensions:



Measurement results:



SOI220nm_1550nm_TE_RIB_90_Degree_Bend

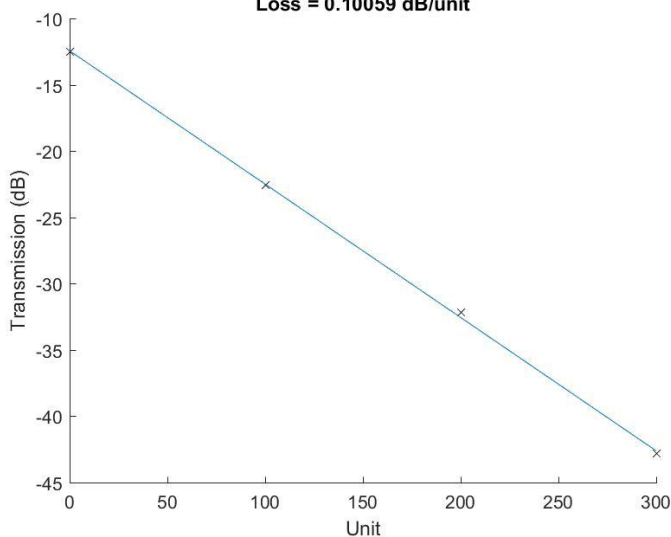
Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	120 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1550nm_TE_RIB_90_Degree_Bend (Waveguide Width (W): 450 nm, Bend Radius (R): 25 μm)

Measurement results on varied dimensions:

(Unit: 90° bend)

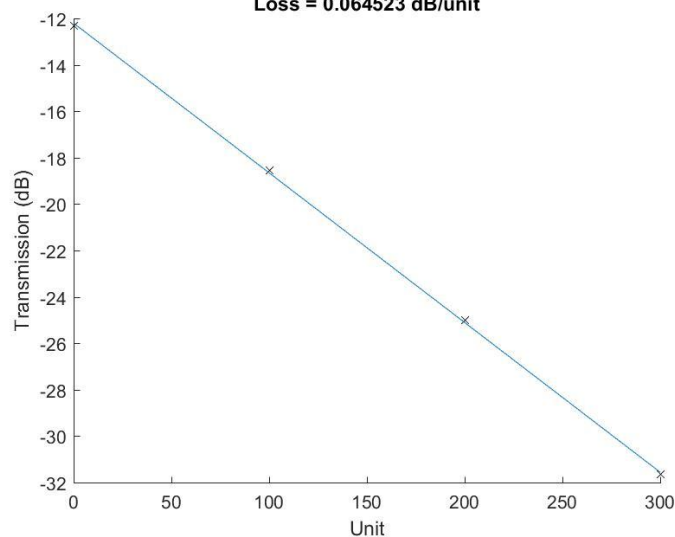
W: 450 nm

Loss = 0.10059 dB/unit

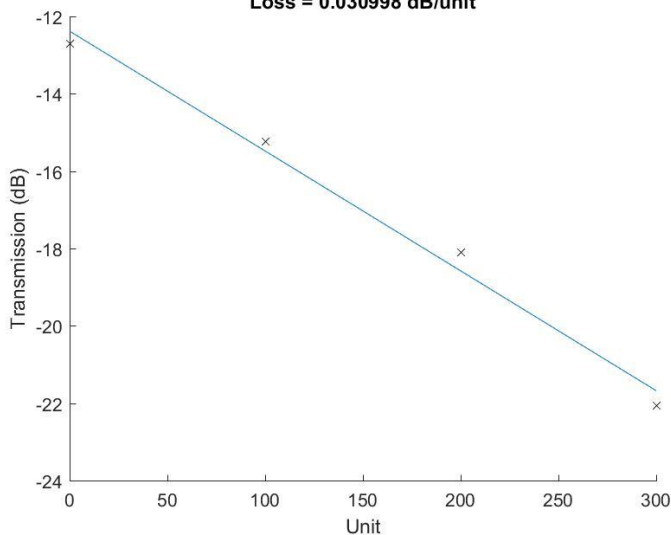


W: 600 nm

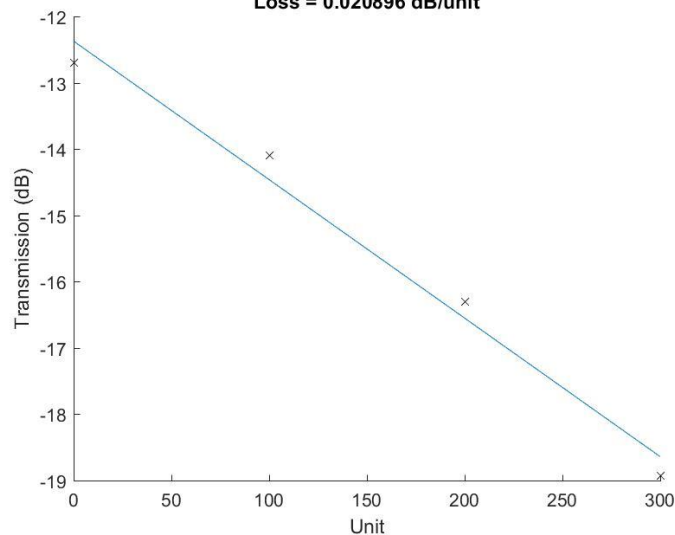
Loss = 0.064523 dB/unit



Loss = 0.030998 dB/unit



Loss = 0.020896 dB/unit



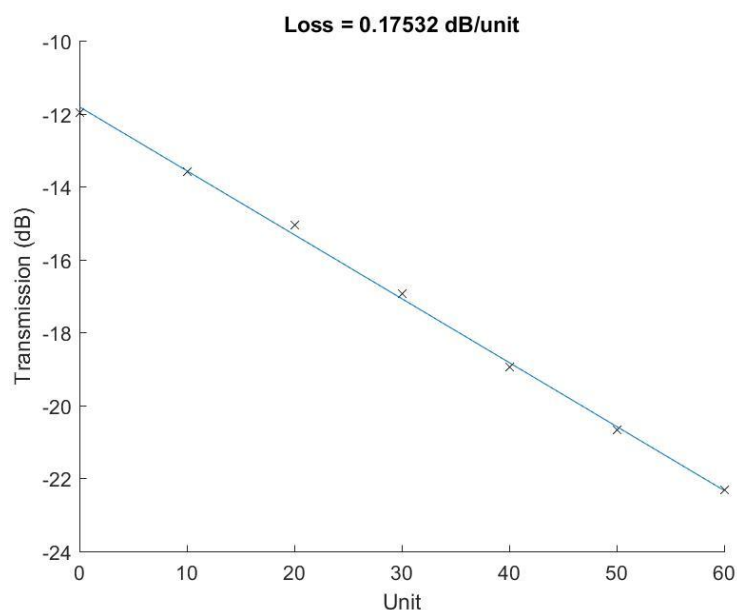
SOI220nm_1550nm_TE_RIB_Waveguide_Crossing

Platform:	220 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	120 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1550nm_TE_RIB_Waveguide_Crossing

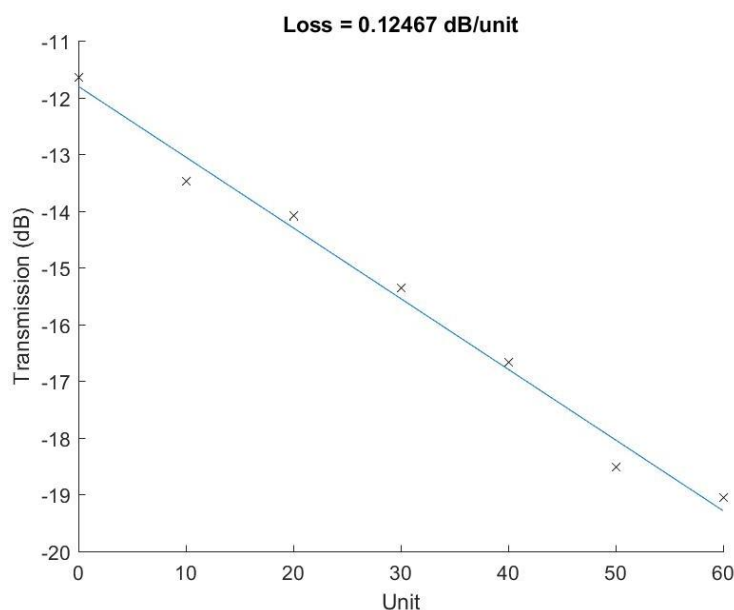
Dimensions: See the drawing in GDS library

Measurement results on different waveguide width (W):

W: 400 nm



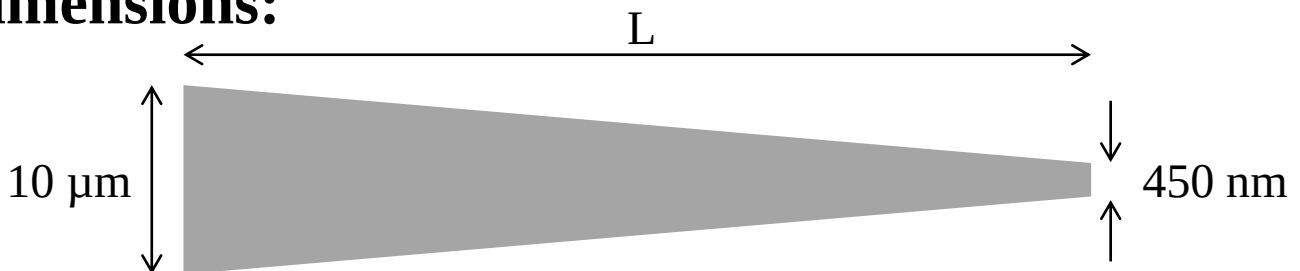
W: 450 nm



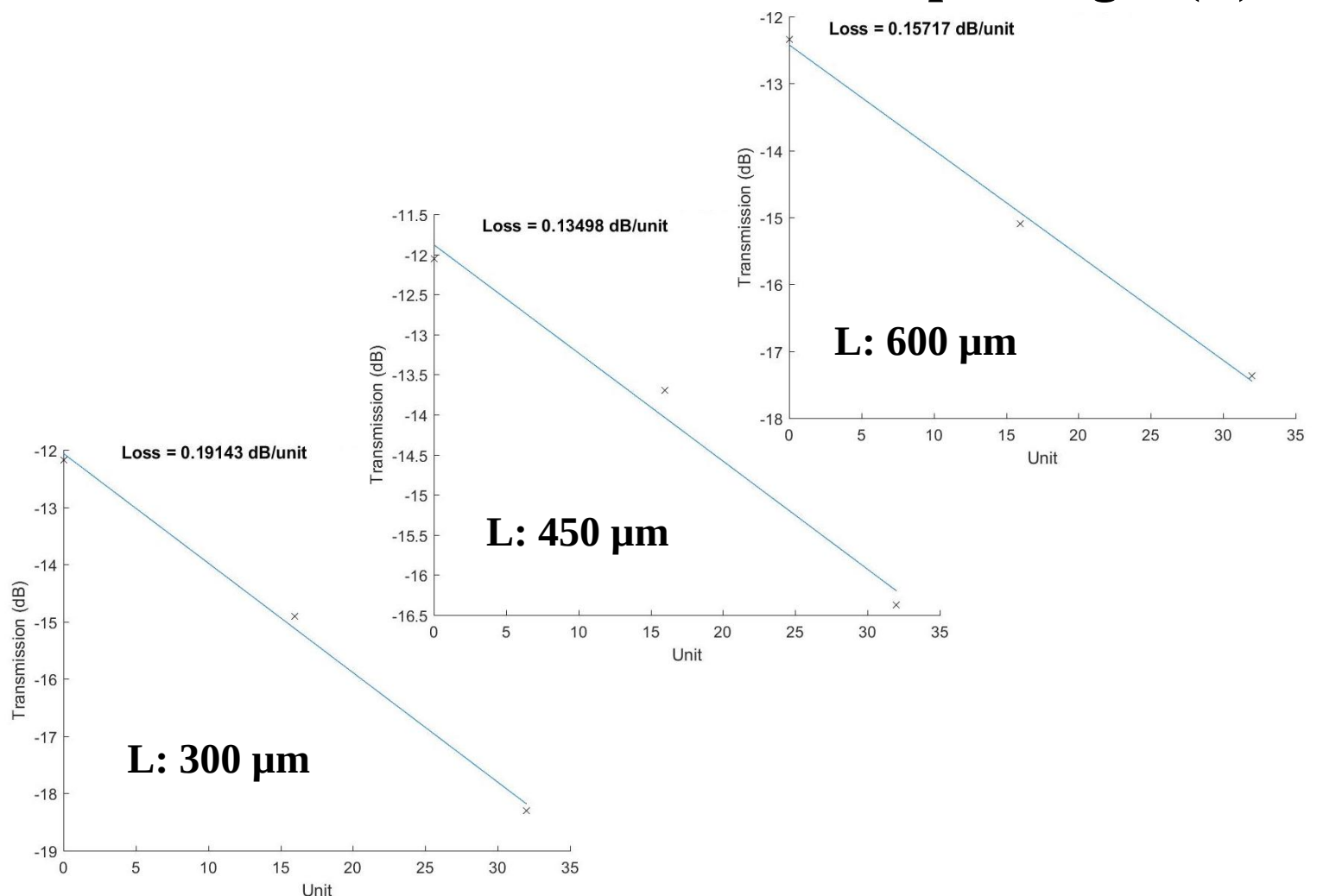
SOI220nm_1550nm_TE_RIB_MM to SM_TAPER

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	120 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	Not in GDS library as an individual component. Used together with grating couplers.

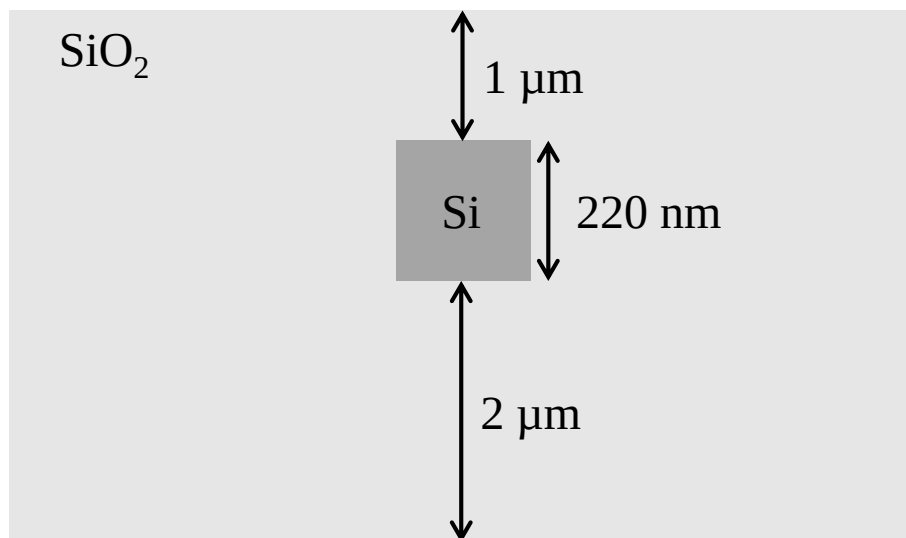
Dimensions:



Measurement results on different taper length (L):



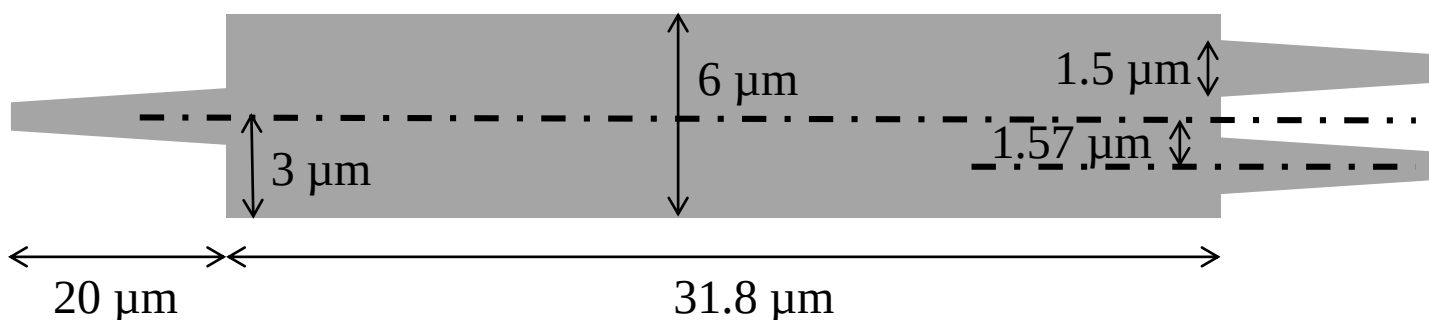
- Wavelength: 1550 nm
- Platform: 220 nm SOI
- **STRIP**



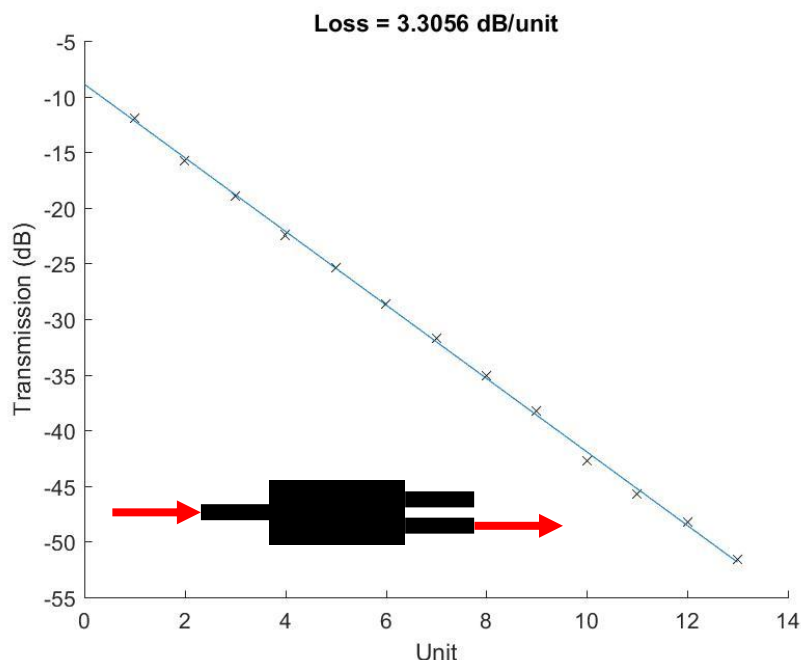
SOI220nm_1550nm_TE_STRIP_2x1_MMI

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1550nm_TE_STRIP_2x1_MMI

Dimensions:



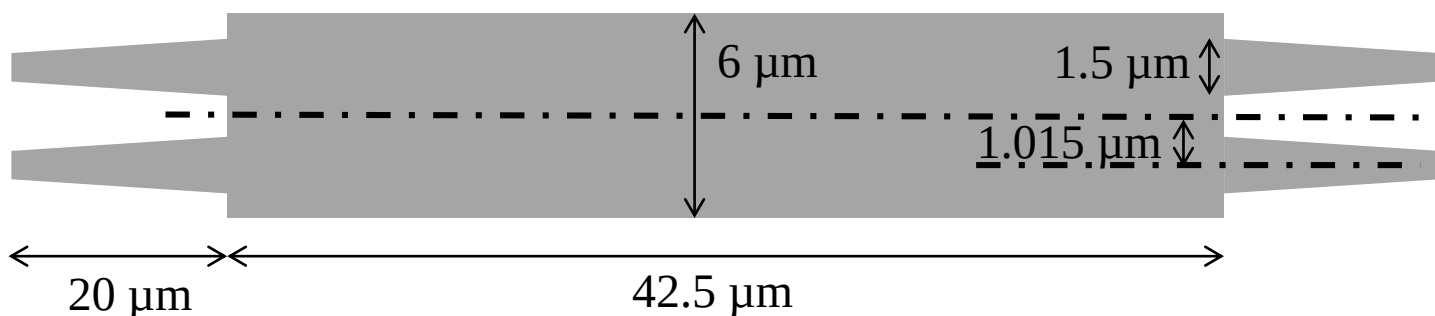
Measurement results:



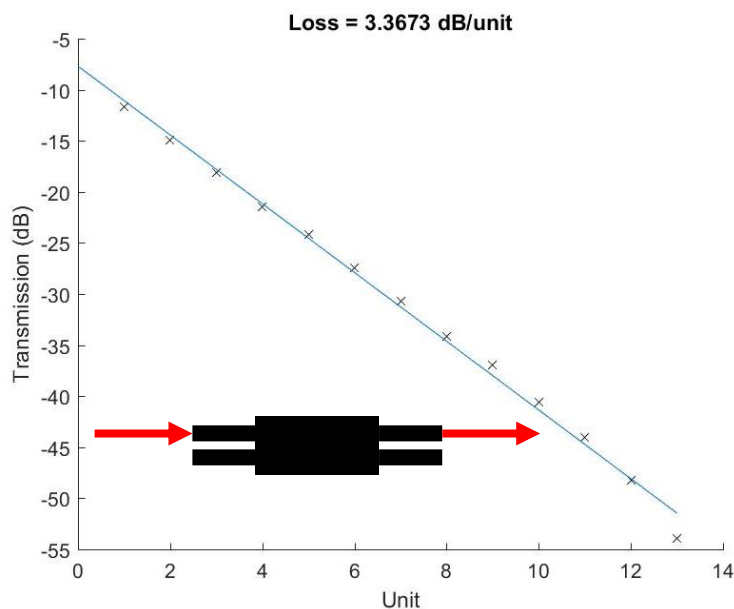
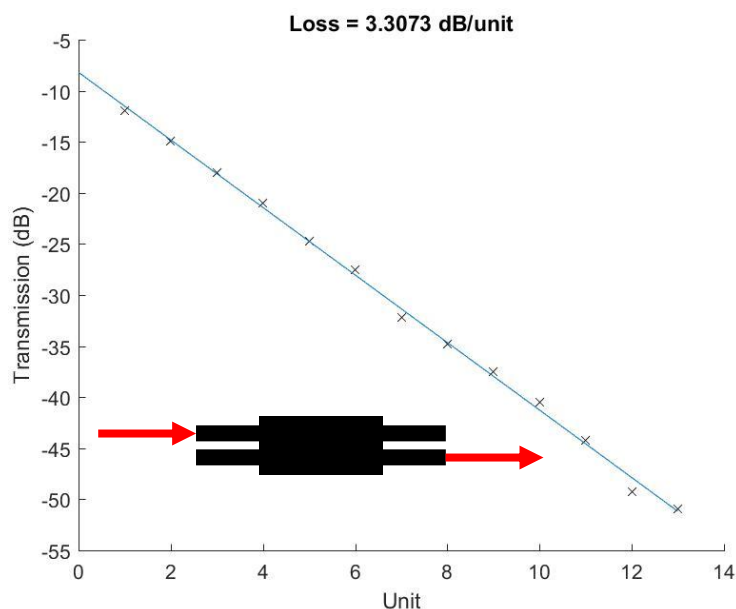
SOI220nm_1550nm_TE_STRIP_2x2_MMI

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1550nm_TE_STRIP_2x2_MMI

Dimensions:



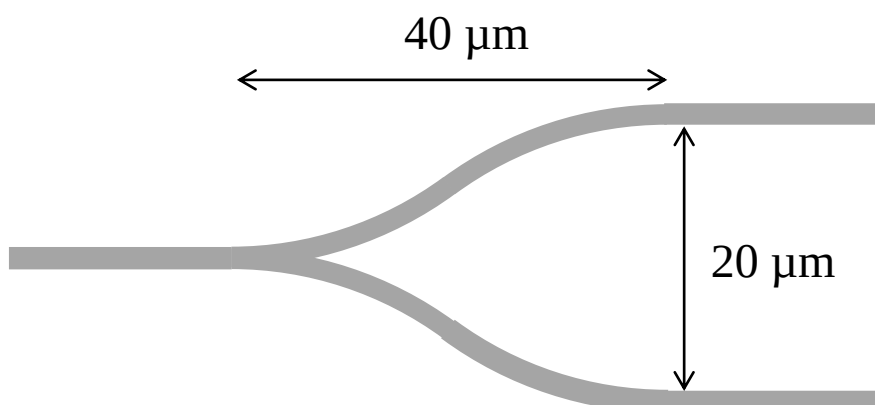
Measurement results:



SOI220nm_1550nm_TE_STRIP_2x1_Ysplitter

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	Not in GDS library

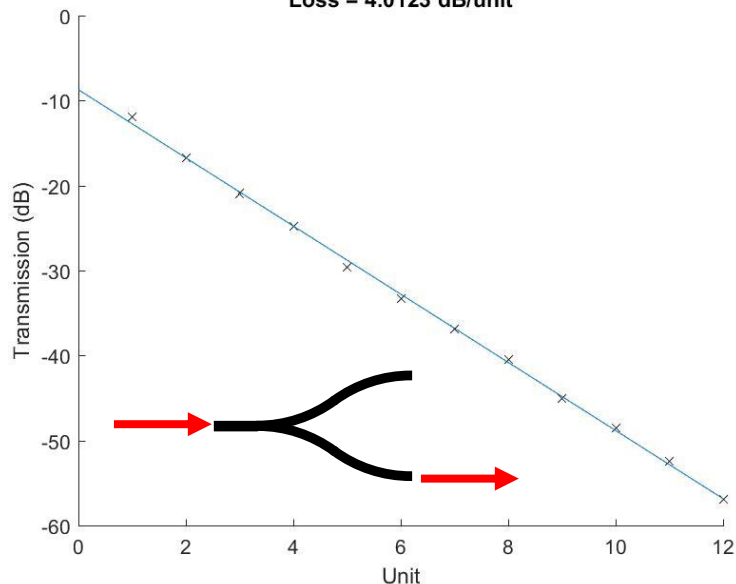
Dimensions:



Measurement results:

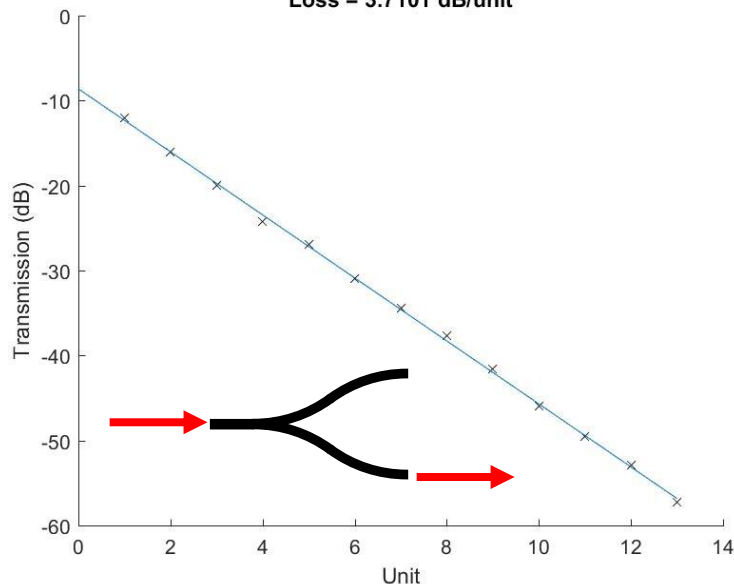
Waveguide width: 450 nm

Loss = 4.0123 dB/unit



Waveguide width: 400 nm

Loss = 3.7101 dB/unit



SOI220nm_1550nm_TE_Strip_90_Degree_Bend

Platform:	220 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1550nm_TE_Strip_90_Degree_Bend (Waveguide Width (W): 450 nm, Bend Radius (R): 5 um)

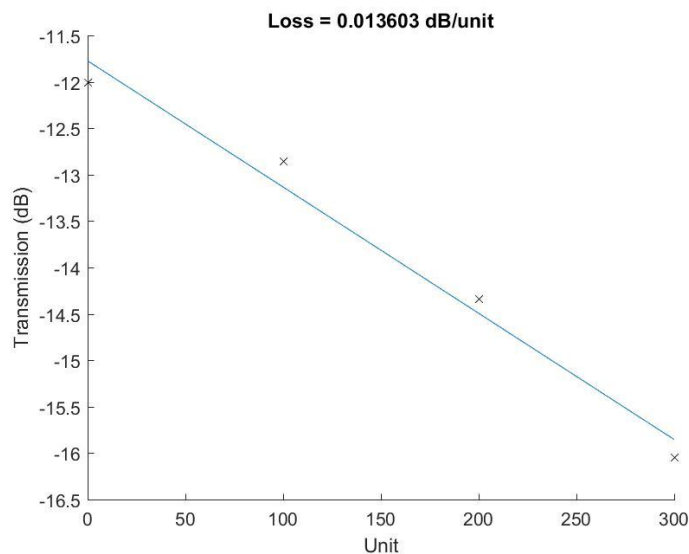
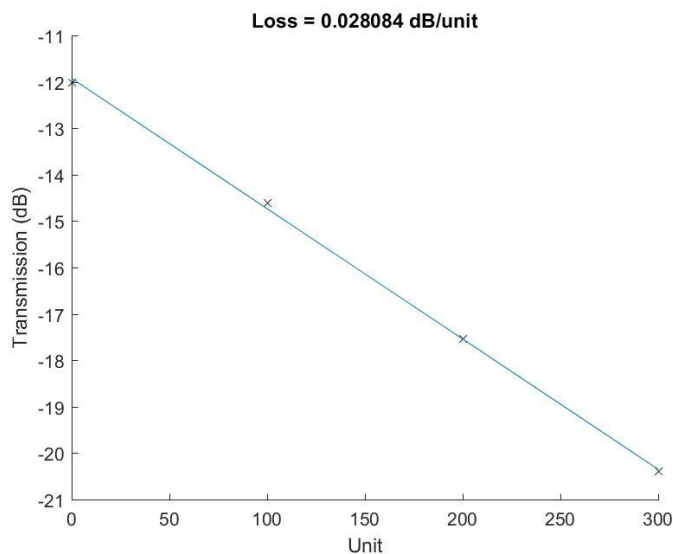
Measurement results on varied dimensions:

(Unit: 90° bend)

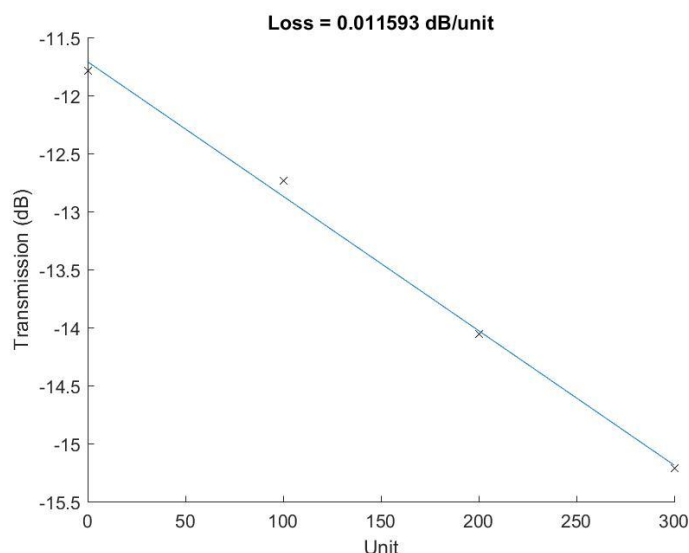
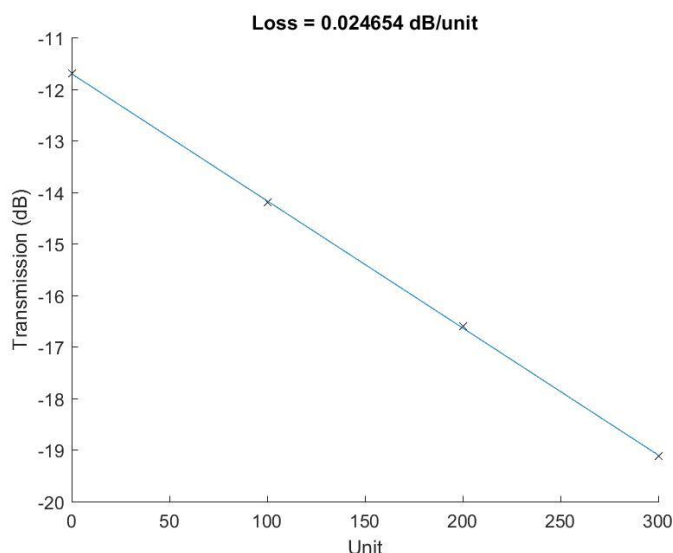
W: 400 nm

W: 450 nm

R: 5 μm



R: 10 μm



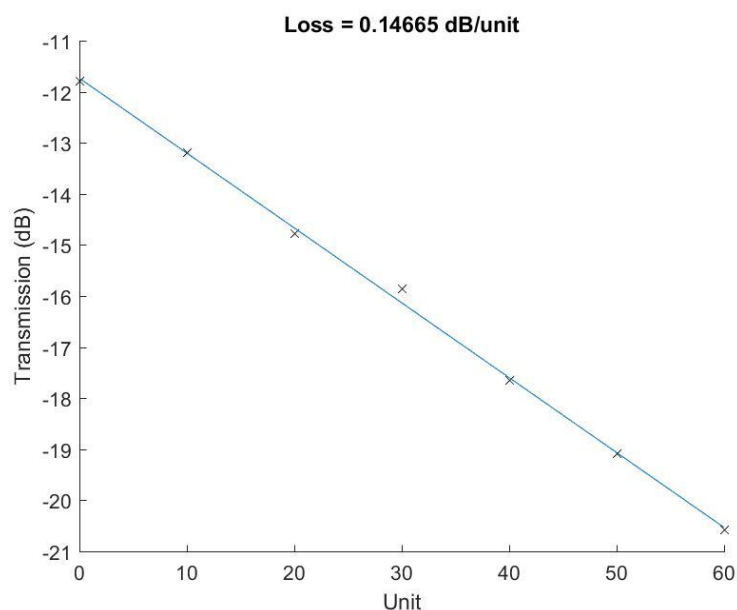
SOI220nm_1550nm_TE_STRIP_Waveguide_Crossing

Platform:	220 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1550nm_TE_STRIP_Waveguide_Crossing

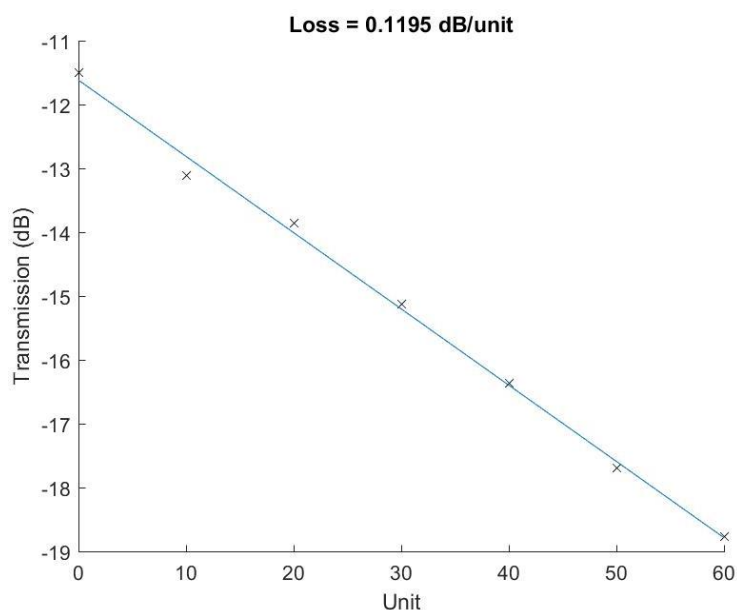
Dimensions: See the drawing in GDS library

Measurement results on different waveguide width (W):

W: 400 nm



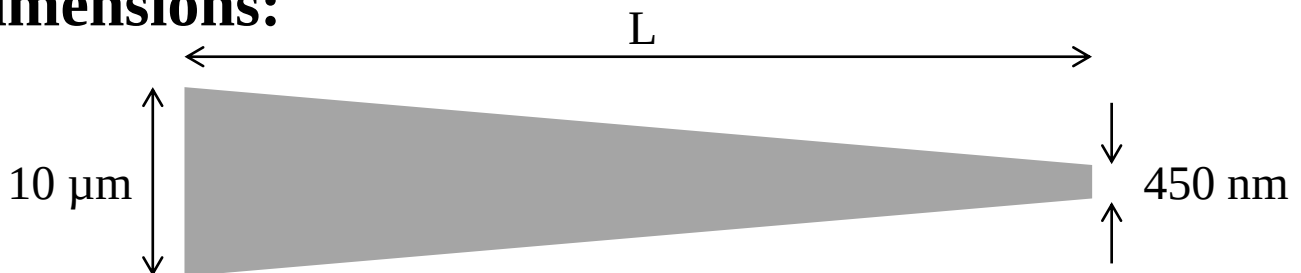
W: 450 nm



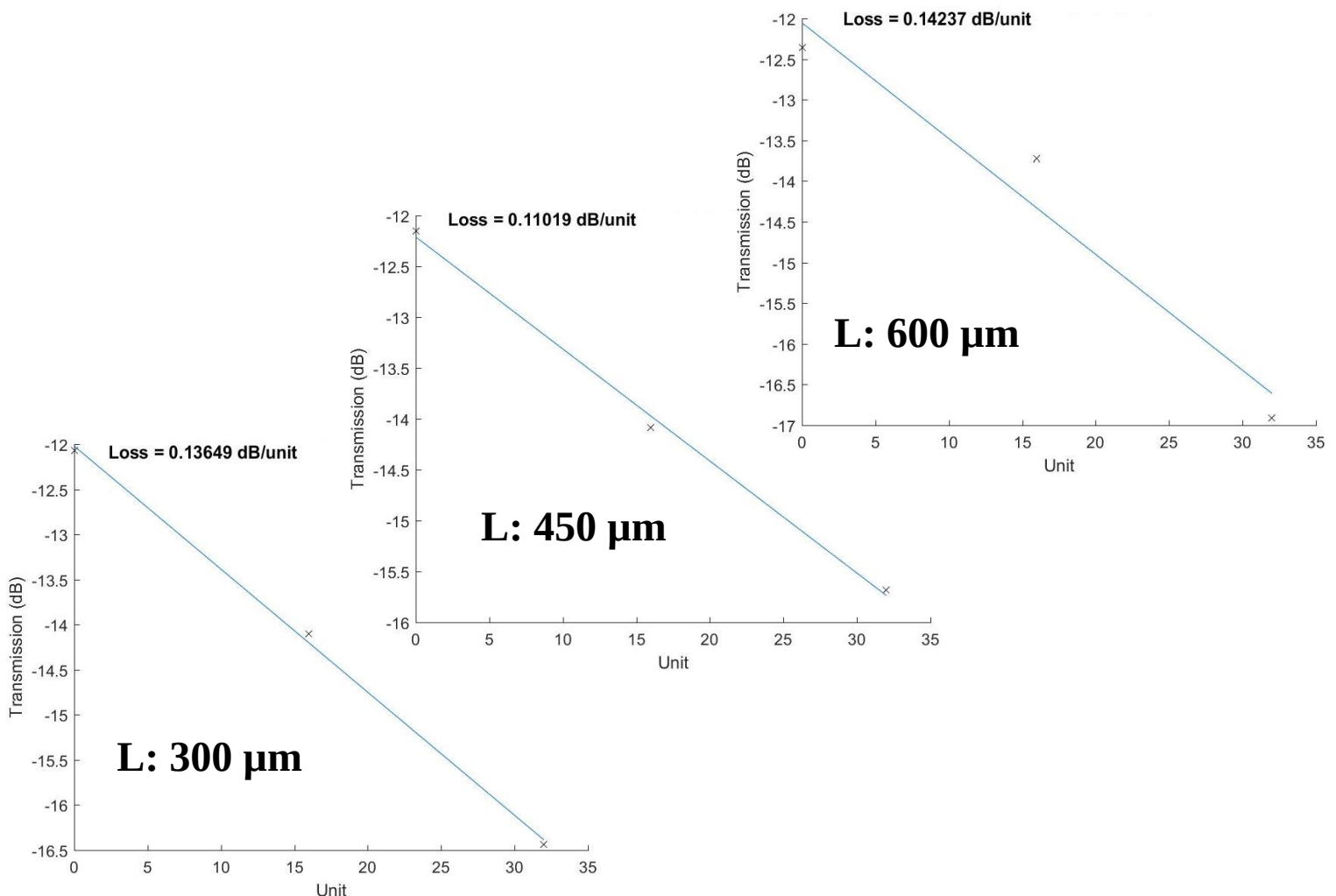
SOI220nm_1550nm_TE_STRIP_MM to SM_TAPER

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	Not in GDS library as an individual component. Used together with grating couplers.

Dimensions:



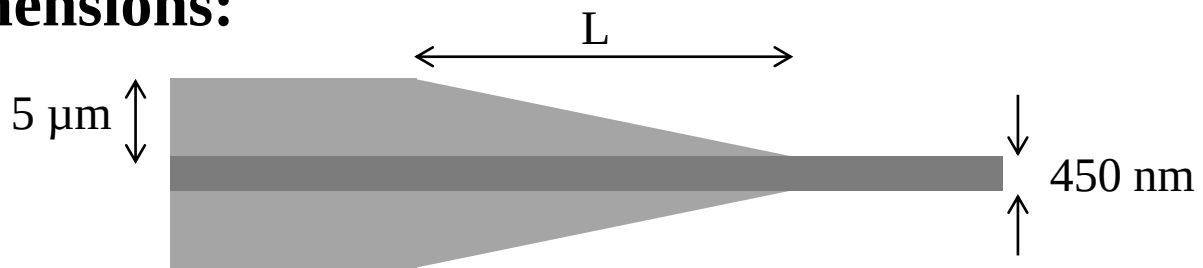
Measurement results on different taper length (L):



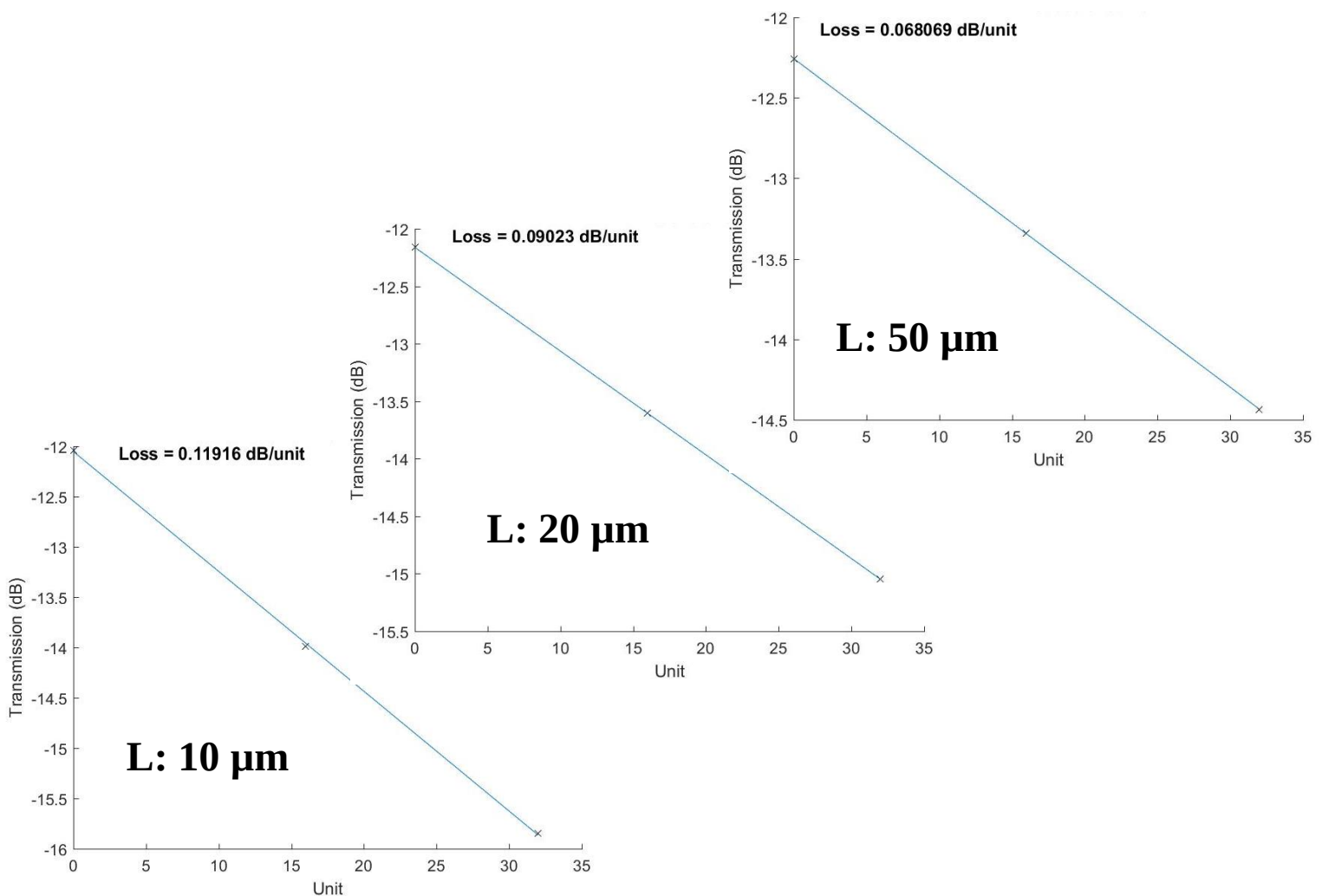
SOI220nm_1550nm_TE_STRIP_RIB to STRIP_TAPER

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	120nm and 220 nm
Polarization:	TE
Cell name in GDS lib:	Not in GDS library.

Dimensions:



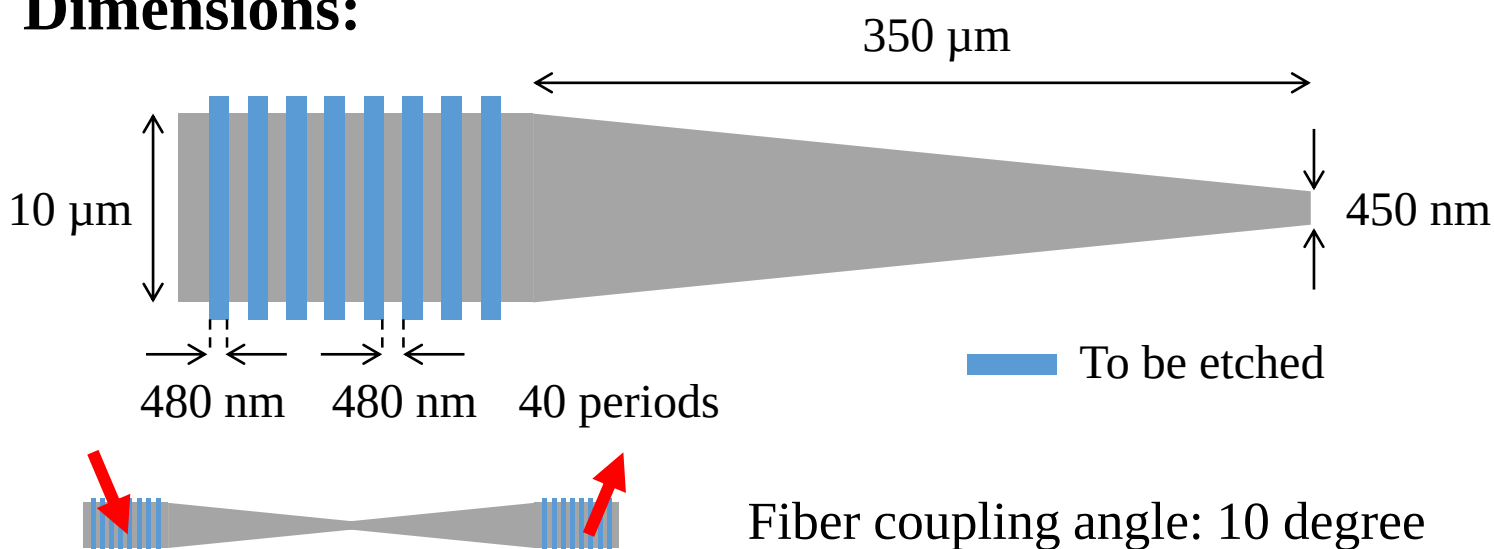
Measurement results on different taper length (L):



SOI220nm_1550nm_TM_STRIP_Grating_Coupler

Platform:	220 nm SOI (2 μ m BOX layer)
Wavelength:	1550 nm
Etching depth:	70 nm (Grating etch depth)
Polarization:	TM
Cell name in GDS lib:	SOI220nm_1550nm_TM_STRIP_Grating_Coupler

Dimensions:



Measured transmission spectrum

Summarized performance:

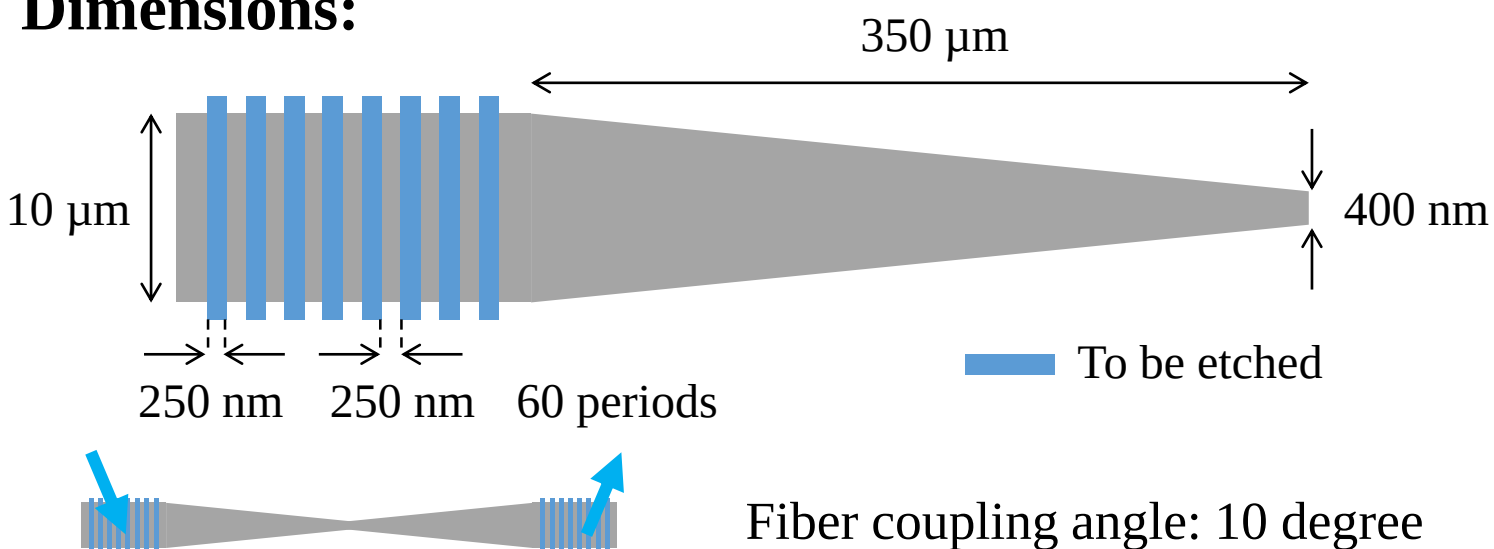
- Coupling efficiency:
dB
- 1 dB bandwidth:
> nm
- Center wavelength:
nm

- **Wavelength: 1310 nm**
- **Platform: 220 nm SOI**

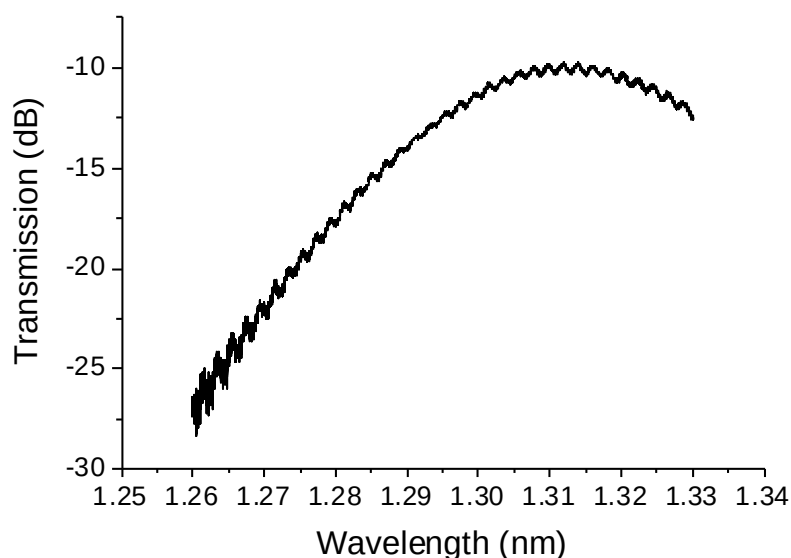
SOI220nm_1310nm_TE_RIB_Grating_Coupler

Platform:	220 nm SOI (2 μ m BOX layer)
Wavelength:	1310 nm
Etching depth:	70 nm (Grating etch depth)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1310nm_TE_RIB_Grating_Coupler

Dimensions:



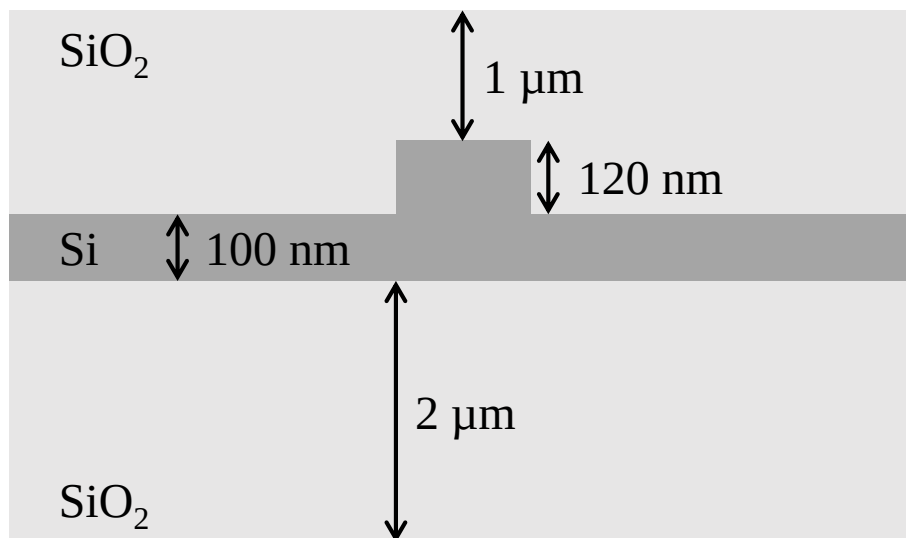
Measured transmission spectrum



Summarized performance:

- Coupling efficiency: 5-6 dB
- 1 dB bandwidth: > 30 nm
- Center wavelength: 1300-1330 nm

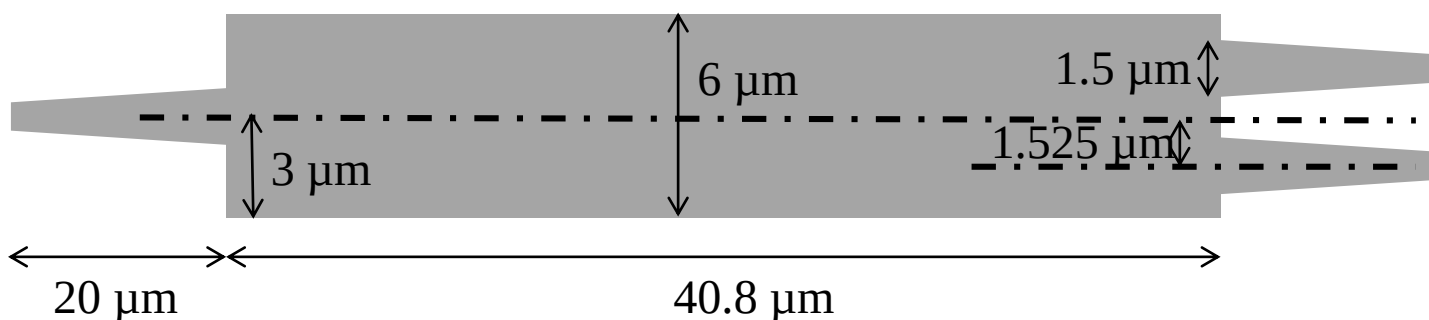
- Wavelength: 1310 nm
- Platform: 220 nm SOI
- **RIB**



SOI220nm_1310nm_TE_RIB_2x1_MMI

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1310 nm
Etching depth:	120 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1310nm_TE_RIB_2x1_MMI

Dimensions:



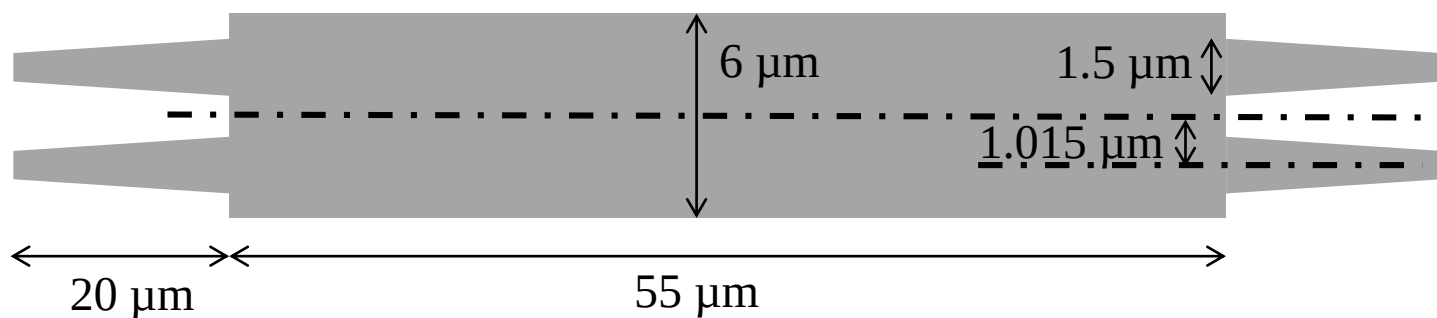
Measurement results:



SOI220nm_1310nm_TE_RIB_2x2_MMI

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	120 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1310nm_TE_RIB_2x2_MMI

Dimensions:



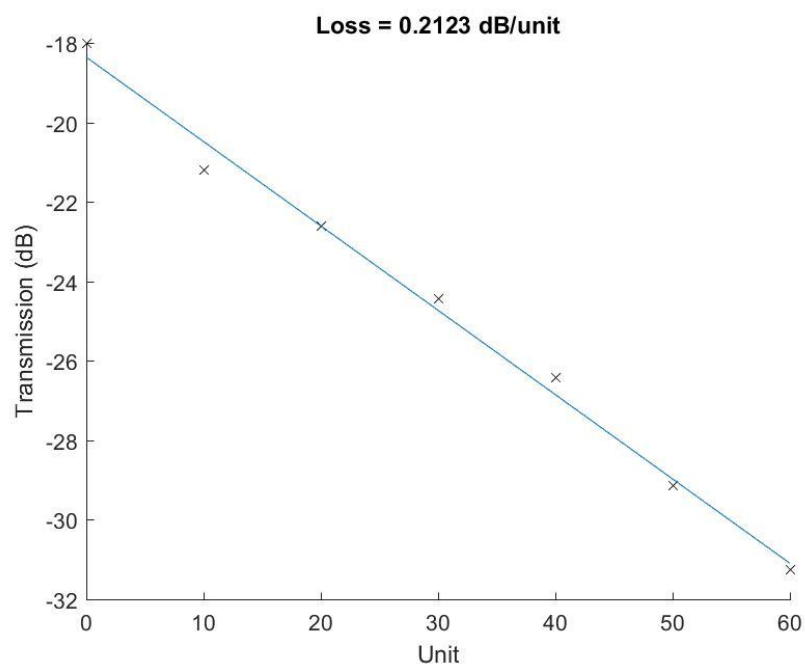
Measurement results:

SOI220nm_1310nm_TE_RIB_Waveguide_Crossing

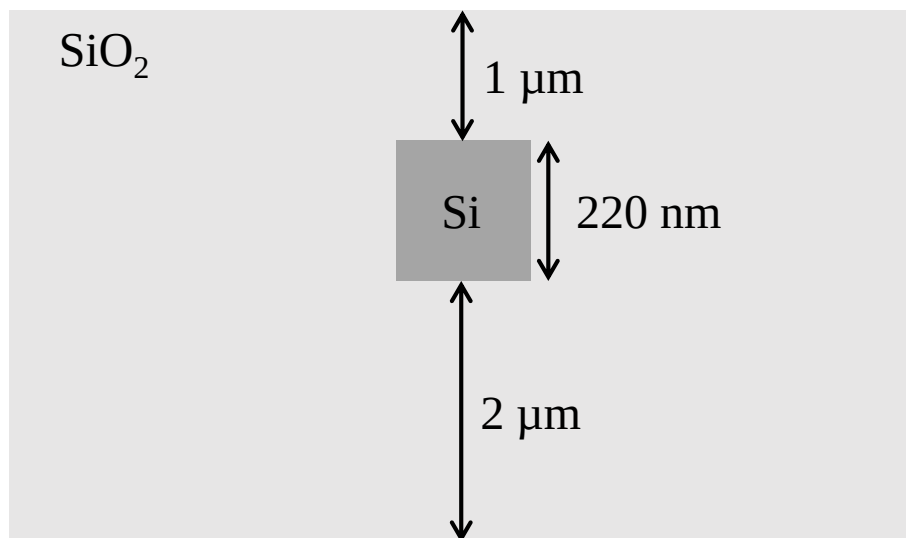
Platform:	220 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	120 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1310nm_TE_RIB_Waveguide_Crossing

Dimensions: See the drawing in GDS library

Measurement results:



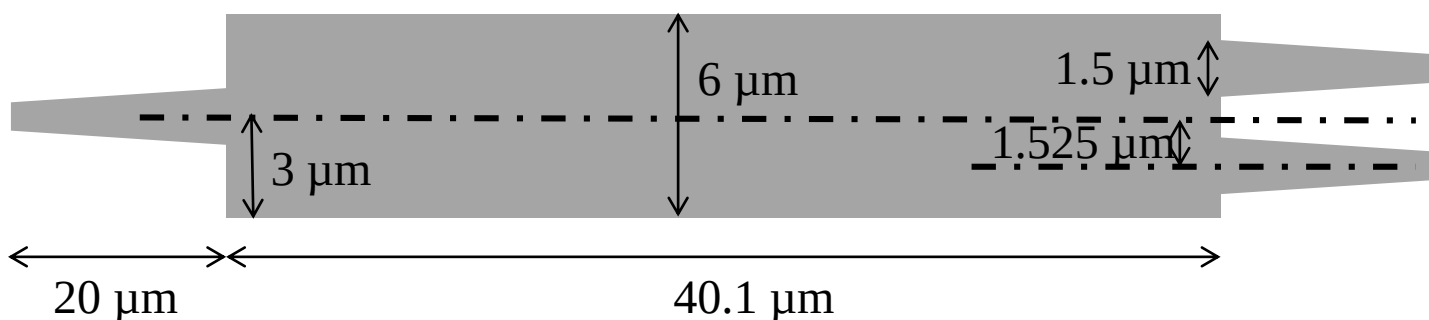
- Wavelength: 1310 nm
- Platform: 220 nm SOI
- **STRIP**



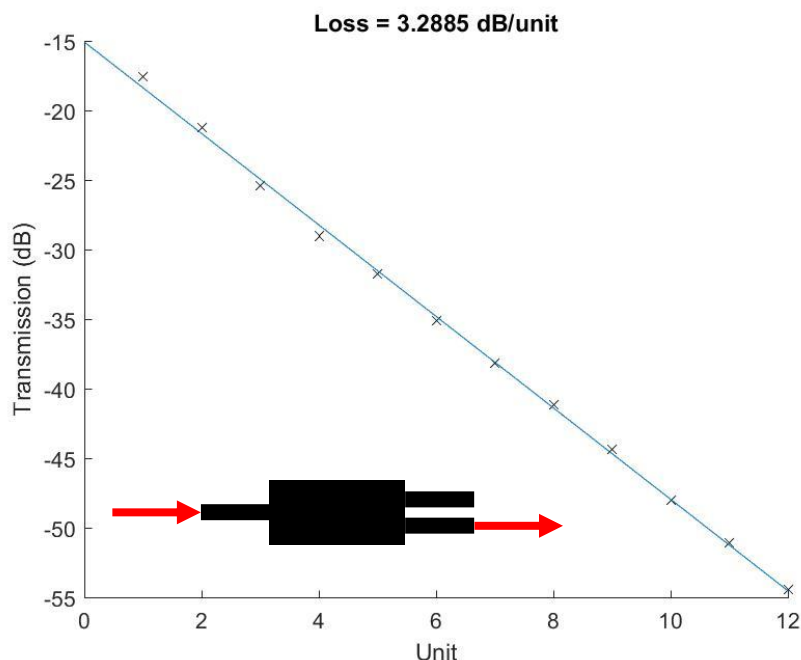
SOI220nm_1310nm_TE_STRIP_2x1_MMI

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1310 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1310nm_TE_STRIP_2x1_MMI

Dimensions:



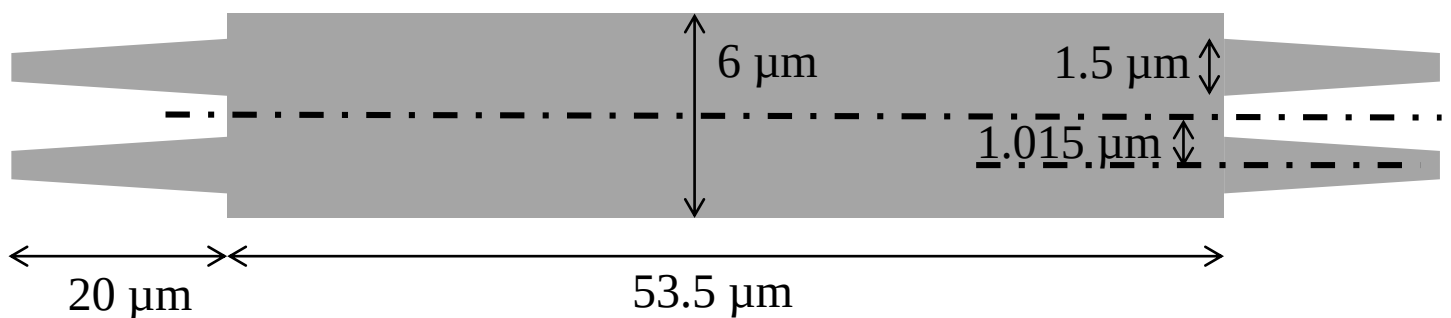
Measurement results:



SOI220nm_1310nm_TE_STRIP_2x2_MMI

Platform:	220 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1310nm_TE_STRIP_2x2_MMI

Dimensions:



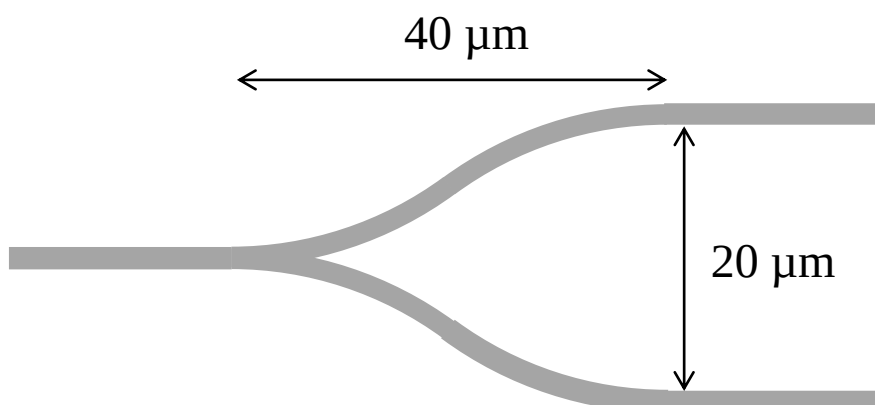
Measurement results:



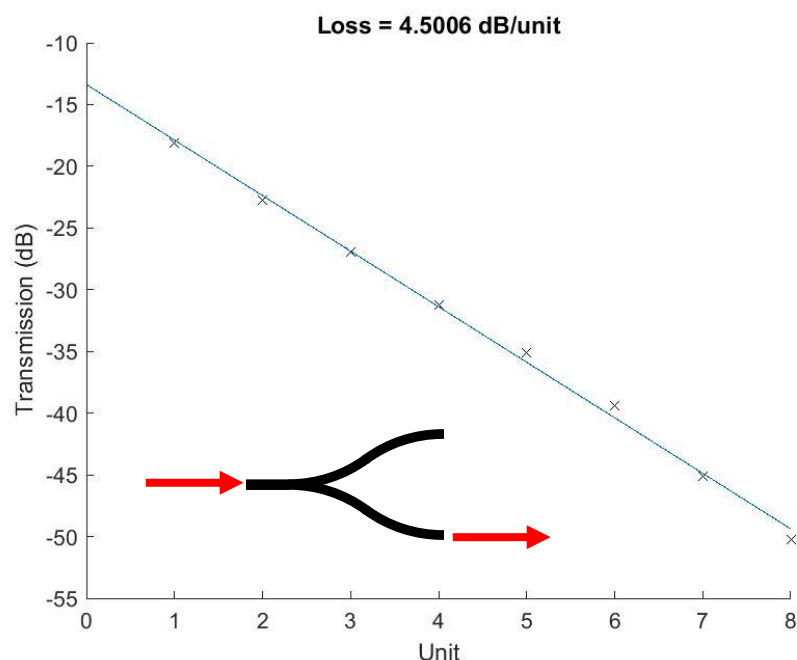
SOI220nm_1310nm_TE_STRIP_2x1_Ysplitter

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1310 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	Not in GDS library

Dimensions:



Measurement results:



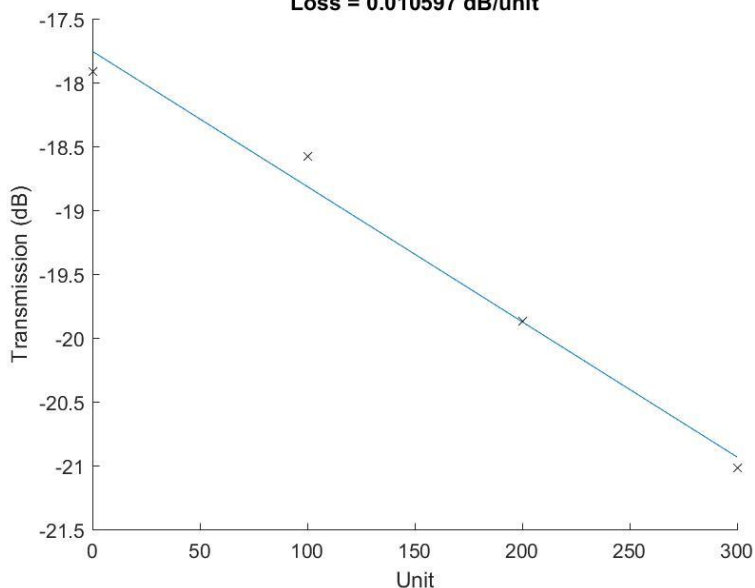
SOI220nm_1310nm_TE_Strip_90_Degree_Bend

Platform:	220 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1310nm_TE_Strip_90_Degree_Bend (Waveguide Width (W): 400 nm, Bend Radius (R): 5 um)

Measurement results on varied dimensions: (Unit: 90° bend)

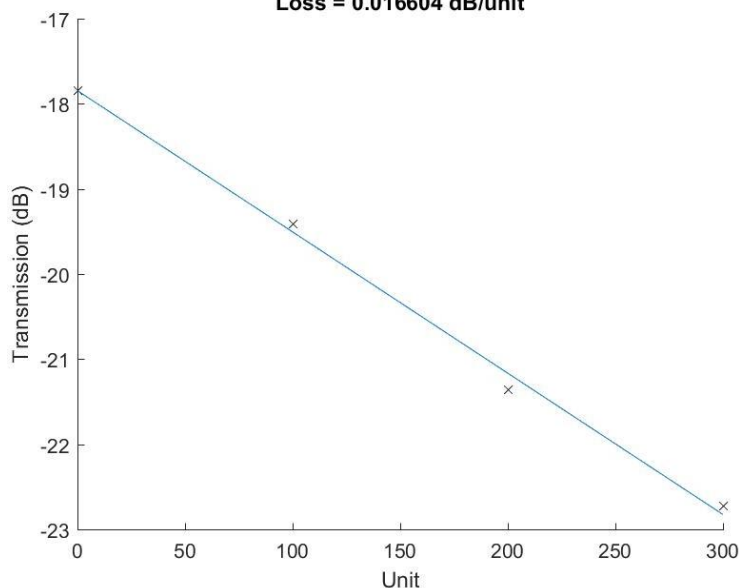
R: 5 μm

Loss = 0.010597 dB/unit



R: 10 μm

Loss = 0.016604 dB/unit

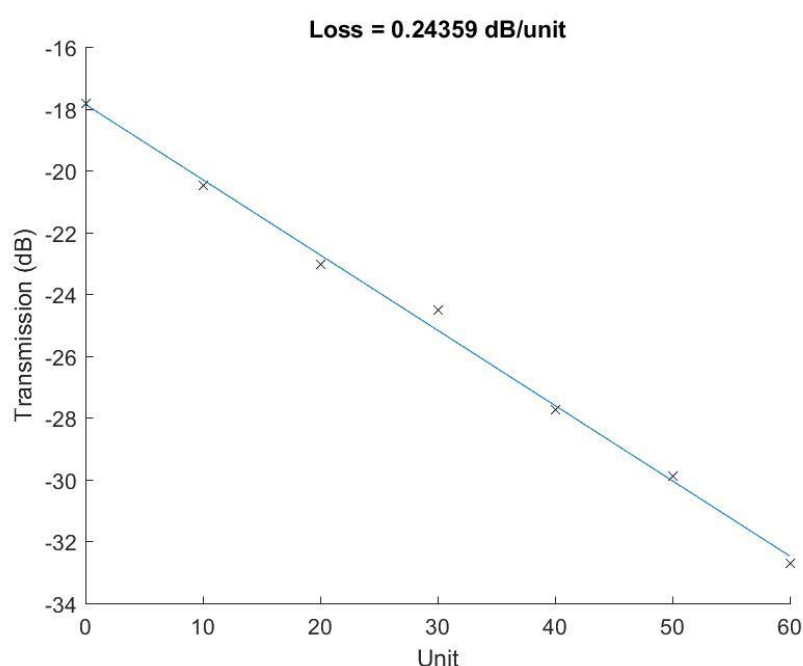


SOI220nm_1310nm_TE_STRIP_Waveguide_Crossing

Platform:	220 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	220 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI220nm_1310nm_TE_STRIP_Waveguide_Crossing

Dimensions: See the drawing in GDS library

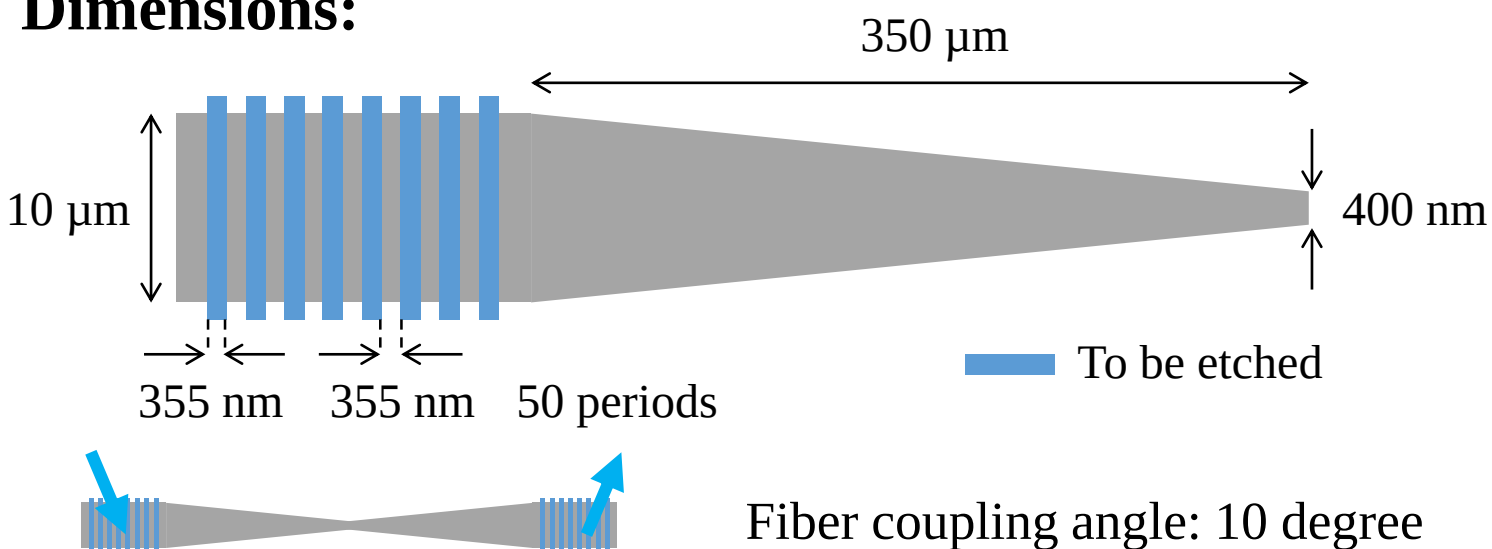
Measurement results:



SOI220nm_1310nm_TM_STRIP_Grating_Coupler

Platform:	220 nm SOI (2 μ m BOX layer)
Wavelength:	1310 nm
Etching depth:	70 nm (Grating etch depth)
Polarization:	TM
Cell name in GDS lib:	SOI220nm_1310nm_TM_STRIP_Grating_Coupler

Dimensions:



Measured transmission spectrum

Summarized performance:

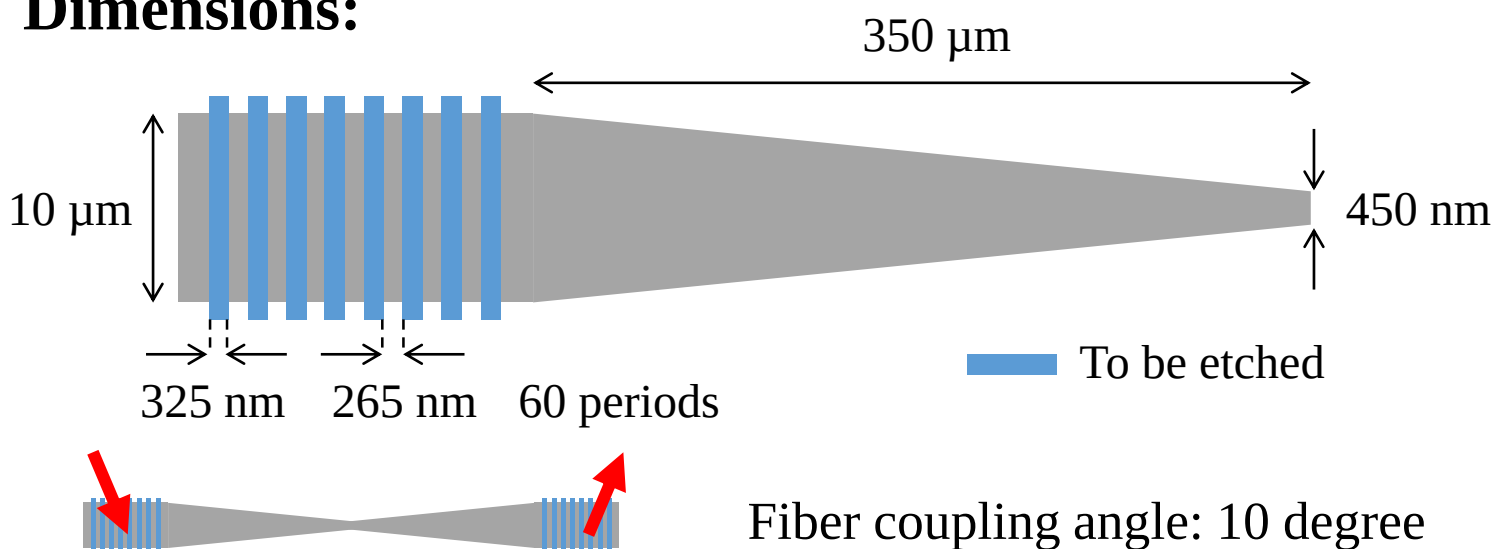
- Coupling efficiency:
dB
- 1 dB bandwidth:
> nm
- Center wavelength:
nm

- **Wavelength: 1550 nm**
- **Platform: 340 nm SOI**

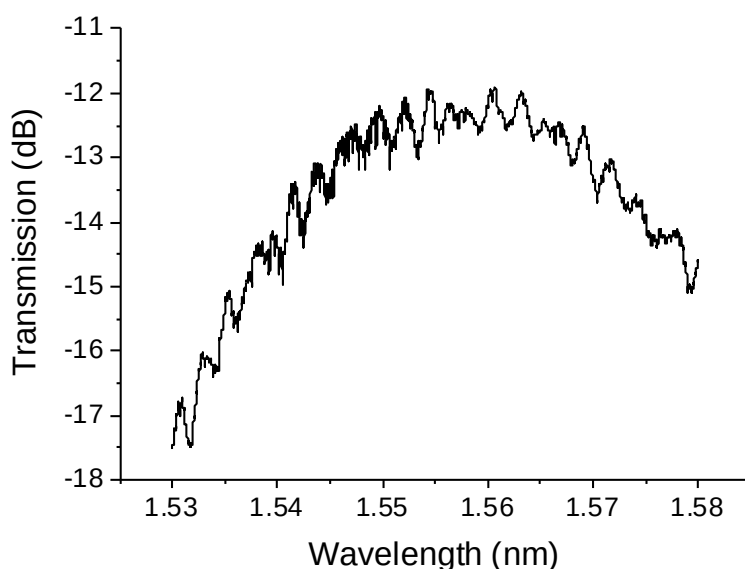
SOI340nm_1550nm_TE_RIB_Grating_Coupler

Platform:	340 nm SOI (2 μ m BOX layer)
Wavelength:	1550 nm
Etching depth:	140 nm (Grating etch depth)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1550nm_TE_RIB_Grating_Coupler

Dimensions:



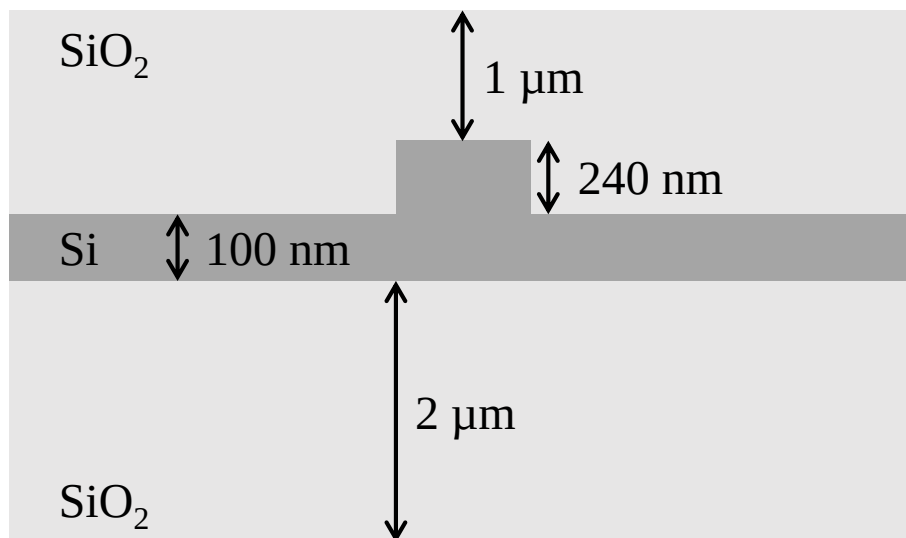
Measured transmission spectrum



Summarized performance:

- Coupling efficiency: 5-7 dB
- 1 dB bandwidth: > 35 nm
- Center wavelength: 1550-1570 nm

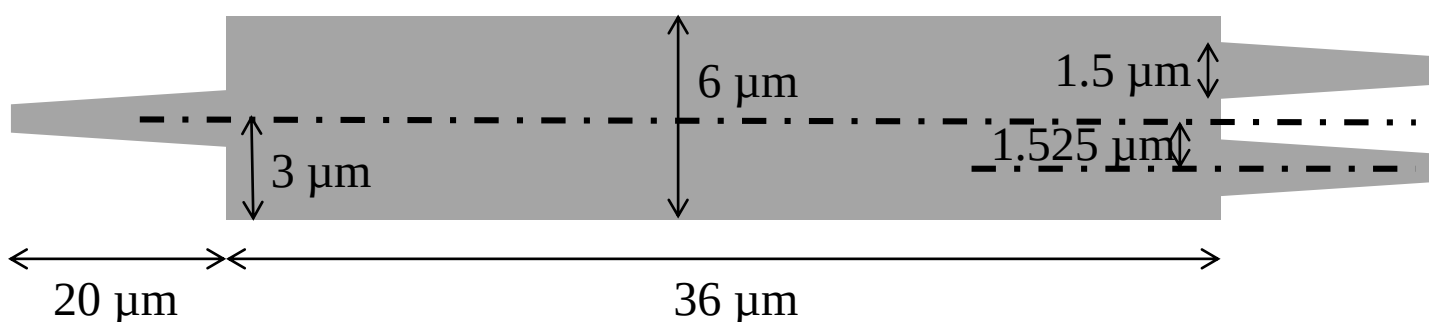
- Wavelength: 1550 nm
- Platform: 340 nm SOI
- **RIB**



SOI340nm_1550nm_TE_RIB_2x1_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	240 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1550nm_TE_RIB_2x1_MMI

Dimensions:

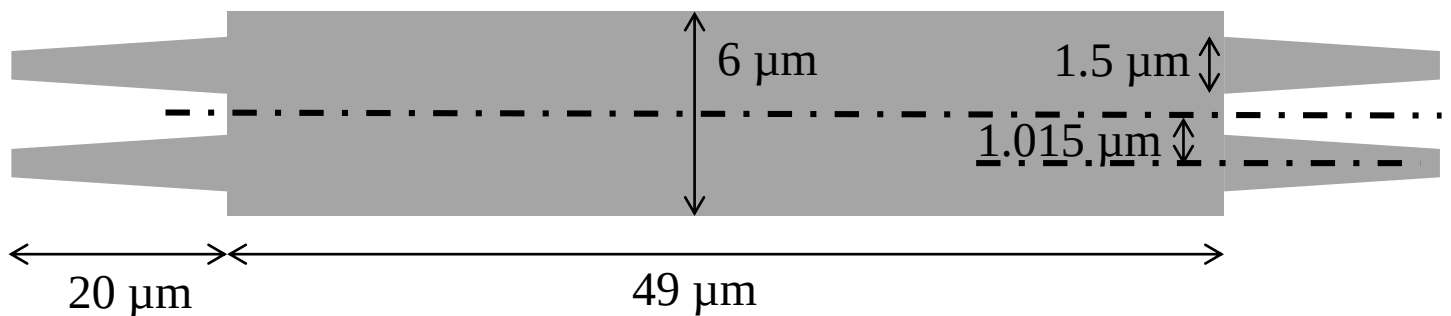


Measurement results:

SOI340nm_1550nm_TE_RIB_2x2_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	240 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1550nm_TE_RIB_2x2_MMI

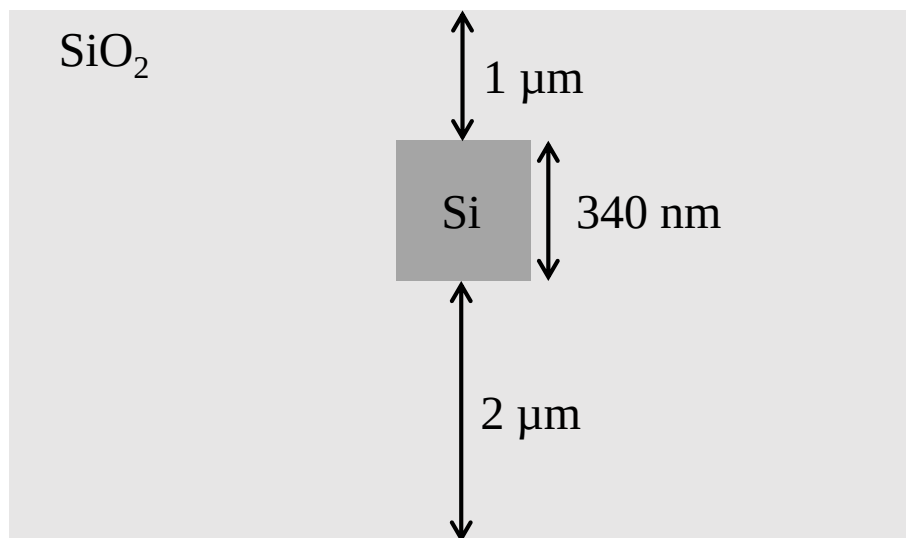
Dimensions:



Measurement results:



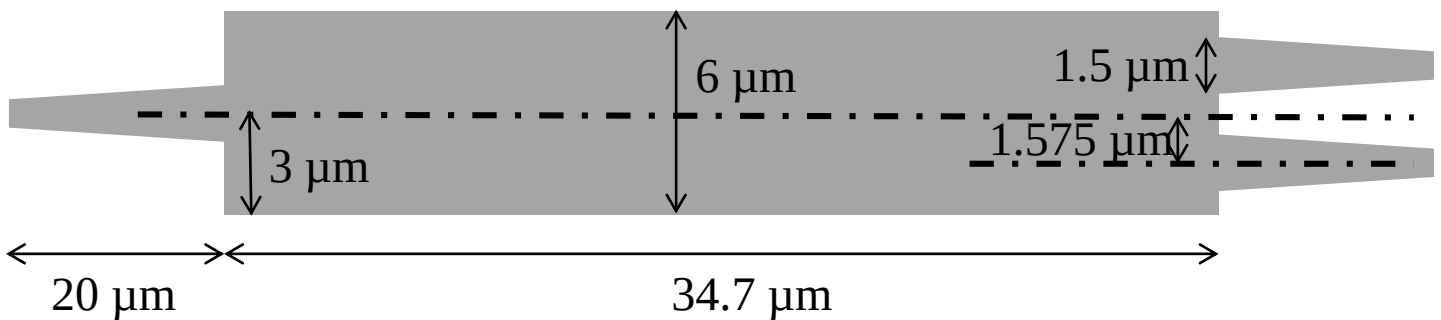
- Wavelength: 1550 nm
- Platform: 340 nm SOI
- **STRIP**



SOI340nm_1550nm_TE_STRIP_2x1_MMI

Platform:	340 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	240 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1550nm_TE_STRIP_2x1_MMI

Dimensions:

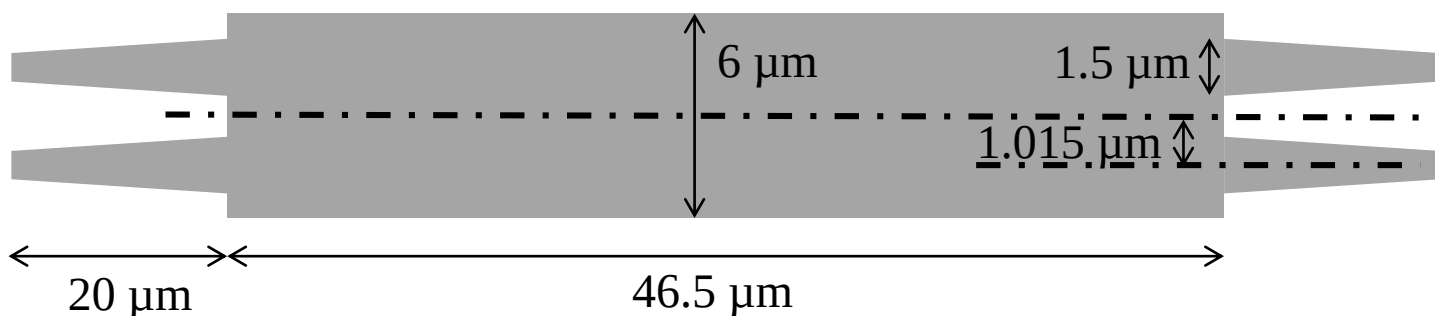


Measurement results:

SOI340nm_1550nm_TE_STRIP_2x2_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	240 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1550nm_TE_STRIP_2x2_MMI

Dimensions:



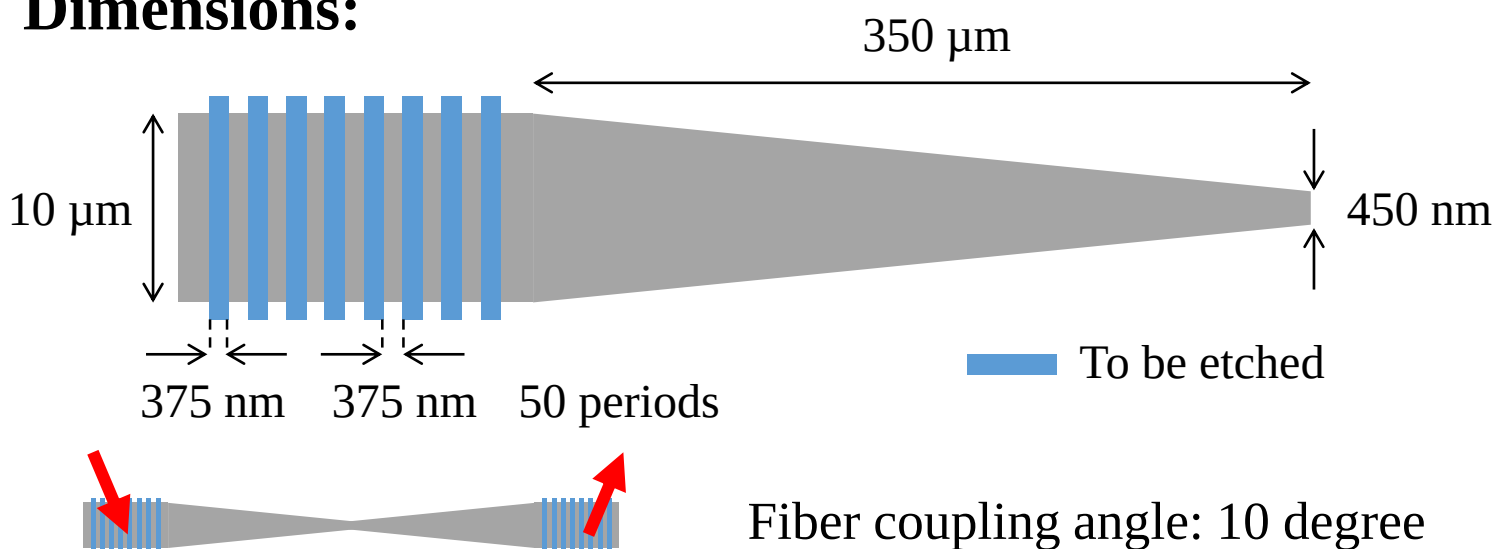
Measurement results:



SOI340nm_1550nm_TM_RIB_Grating_Coupler

Platform:	340 nm SOI (2 μ m BOX layer)
Wavelength:	1550 nm
Etching depth:	140 nm (Grating etch depth)
Polarization:	TM
Cell name in GDS lib:	SOI340nm_1550nm_TM_RIB_Grating_Coupler

Dimensions:



Measured transmission spectrum

Summarized performance:

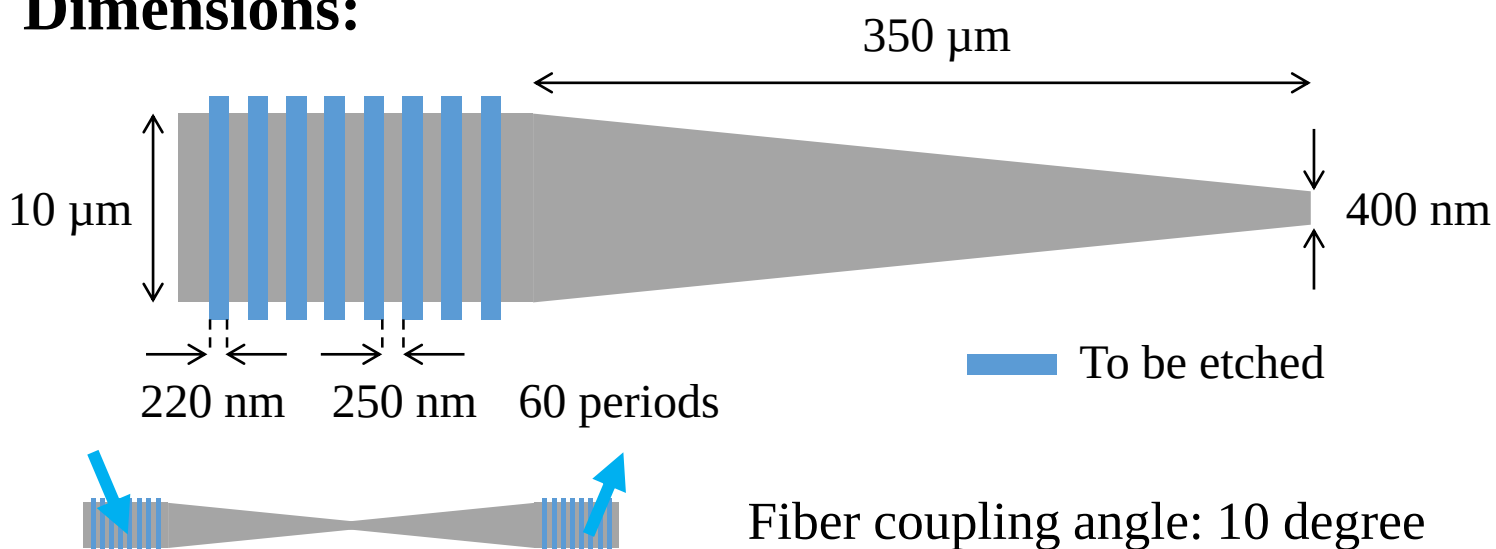
- Coupling efficiency:
dB
- 1 dB bandwidth:
> nm
- Center wavelength:
nm

- **Wavelength: 1310 nm**
- **Platform: 340 nm SOI**

SOI340nm_1310nm_TE_RIB_Grating_Coupler

Platform:	340 nm SOI (2 μ m BOX layer)
Wavelength:	1310 nm
Etching depth:	140 nm (Grating etch depth)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1310nm_TE_RIB_Grating_Coupler

Dimensions:

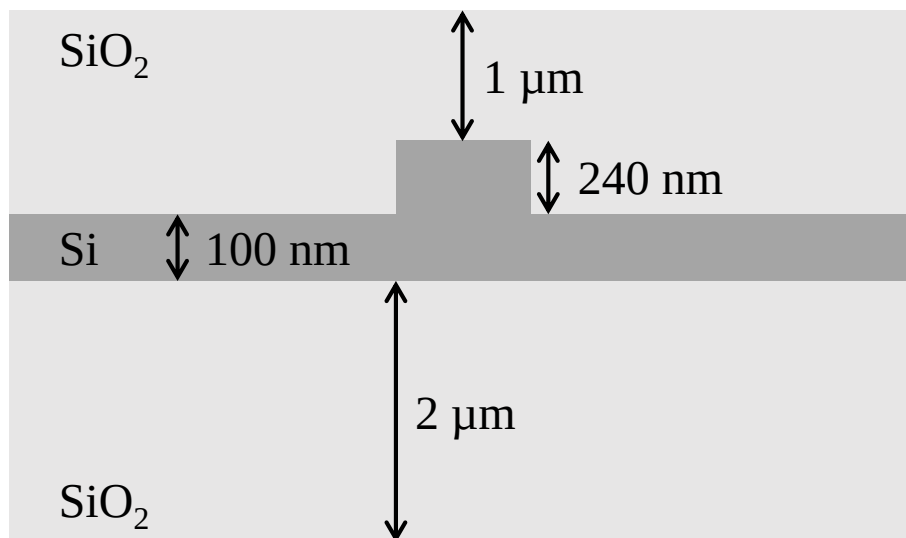


Measured transmission spectrum

Summarized performance:

- Coupling efficiency:
dB
- 1 dB bandwidth:
> nm
- Center wavelength:
nm

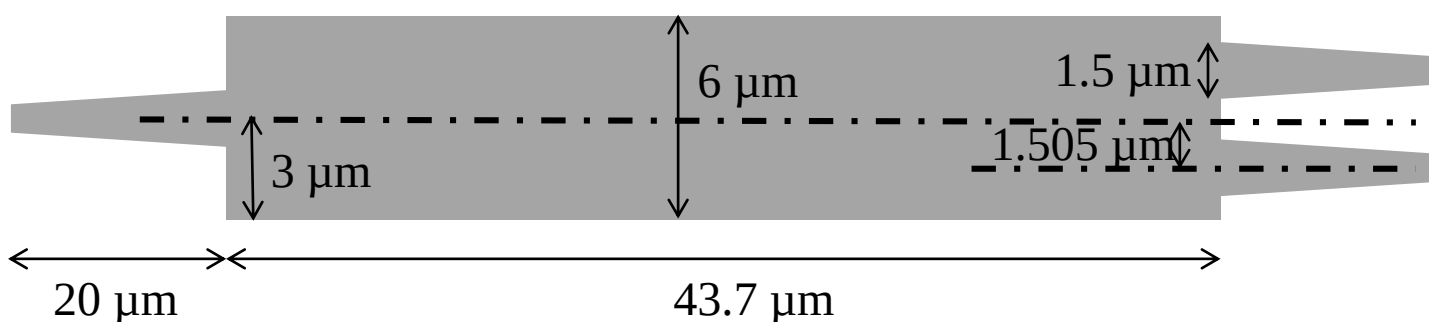
- Wavelength: 1310 nm
- Platform: 340 nm SOI
- **RIB**



SOI340nm_1310nm_TE_RIB_2x1_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	240 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1310nm_TE_RIB_2x1_MMI

Dimensions:

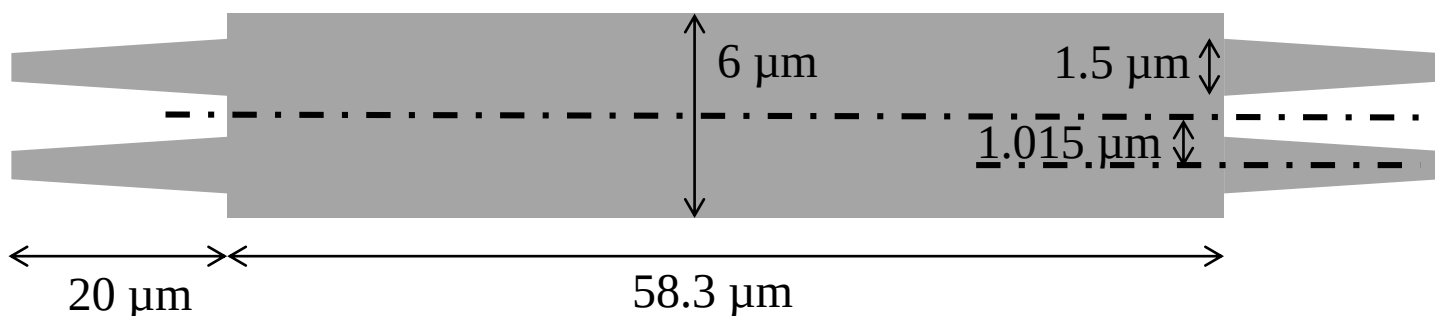


Measurement results:

SOI340nm_1310nm_TE_RIB_2x2_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	240 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1310nm_TE_RIB_2x2_MMI

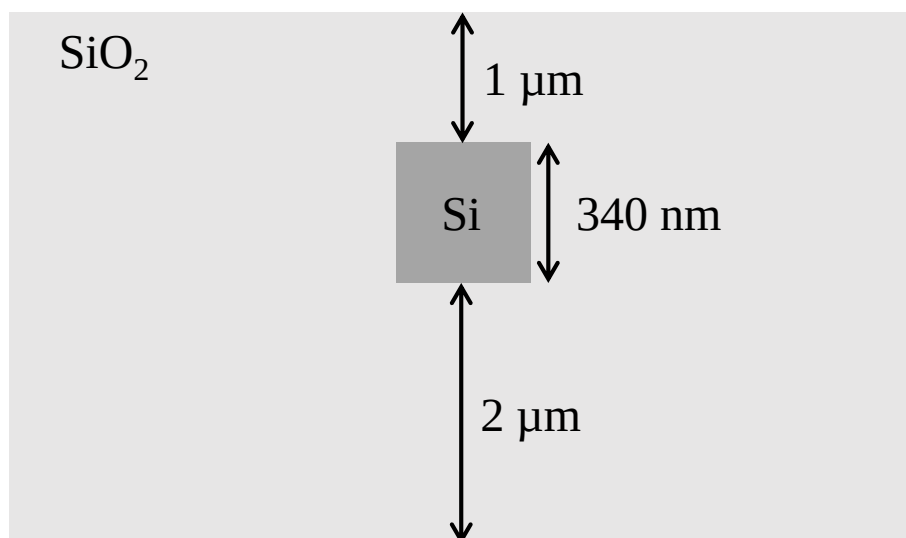
Dimensions:



Measurement results:



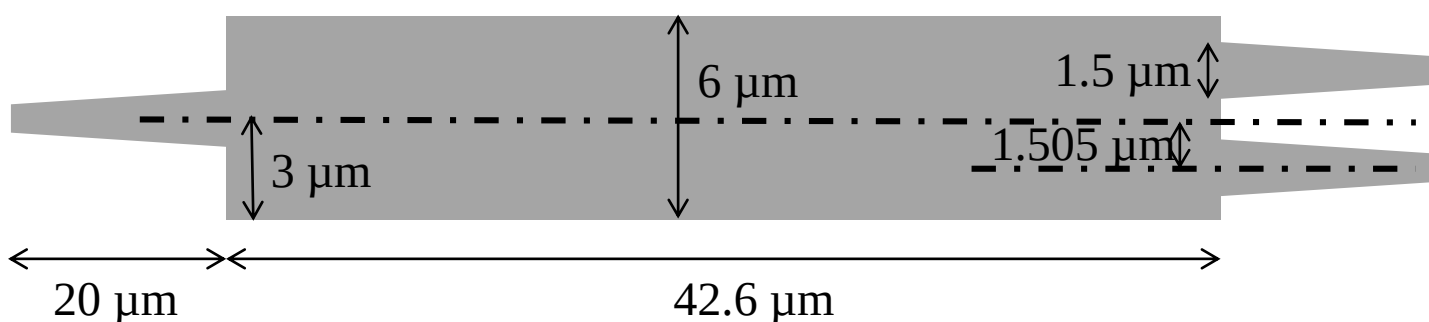
- Wavelength: 1310 nm
- Platform: 340 nm SOI
- **STRIP**



SOI340nm_1310nm_TE_STRIP_2x1_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	340 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1310nm_TE_STRIP_2x1_MMI

Dimensions:

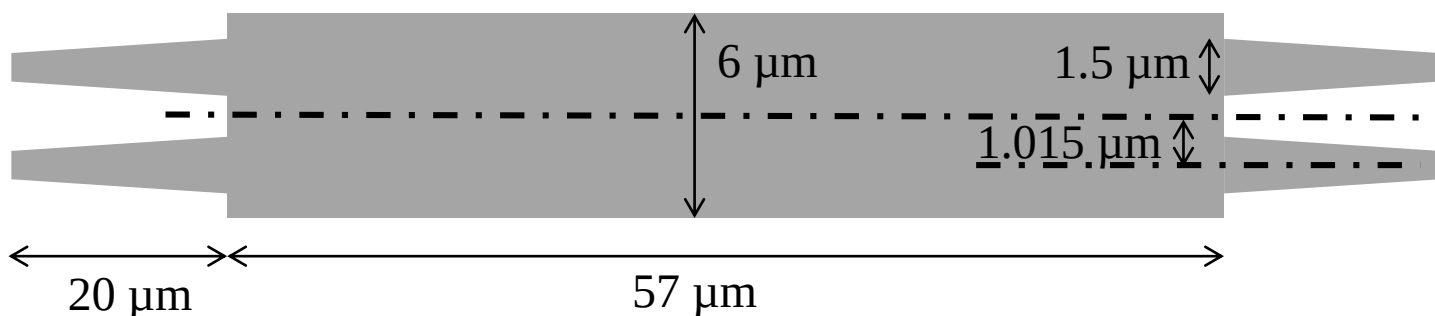


Measurement results:

SOI340nm_1310nm_TE_STRIP_2x2_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	340 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1310nm_TE_STRIP_2x2_MMI

Dimensions:



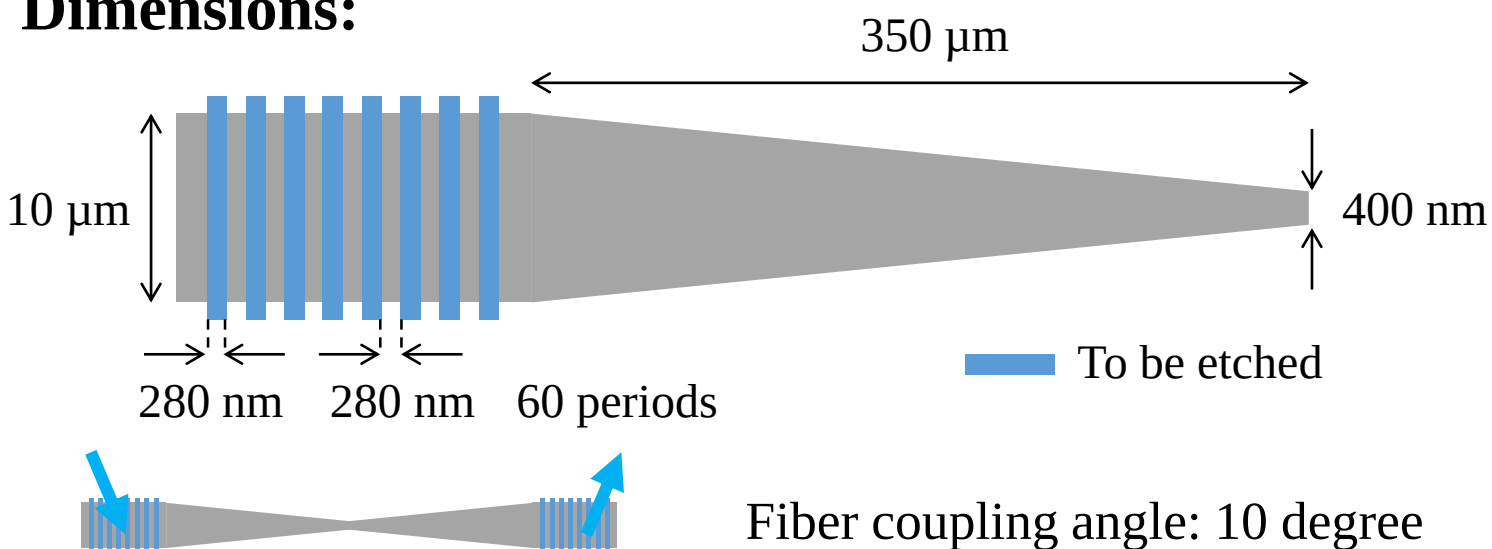
Measurement results:



SOI340nm_1310nm_TM_RIB_Grating_Coupler

Platform:	340 nm SOI (2 μ m BOX layer)
Wavelength:	1310 nm
Etching depth:	140 nm (Grating etch depth)
Polarization:	TM
Cell name in GDS lib:	SOI340nm_1310nm_TM_RIB_Grating_Coupler

Dimensions:



Measured transmission spectrum

Summarized performance:

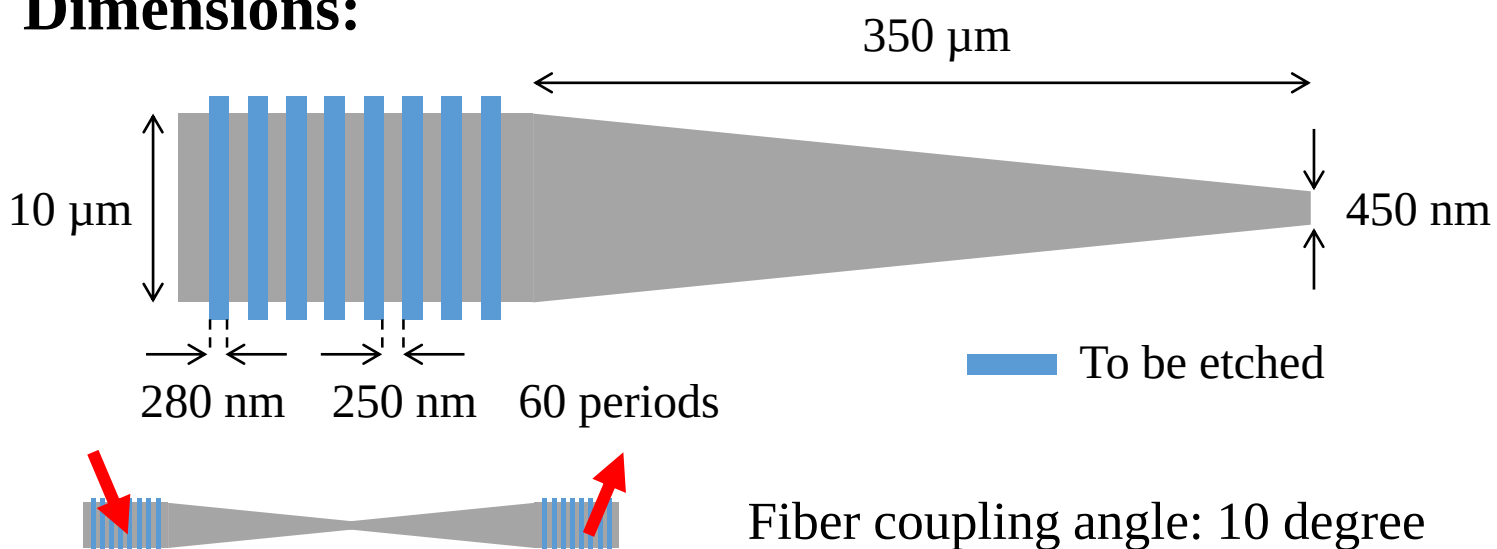
- Coupling efficiency:
dB
- 1 dB bandwidth:
> nm
- Center wavelength:
nm

- **Wavelength: 1550 nm**
- **Platform: 500 nm SOI**

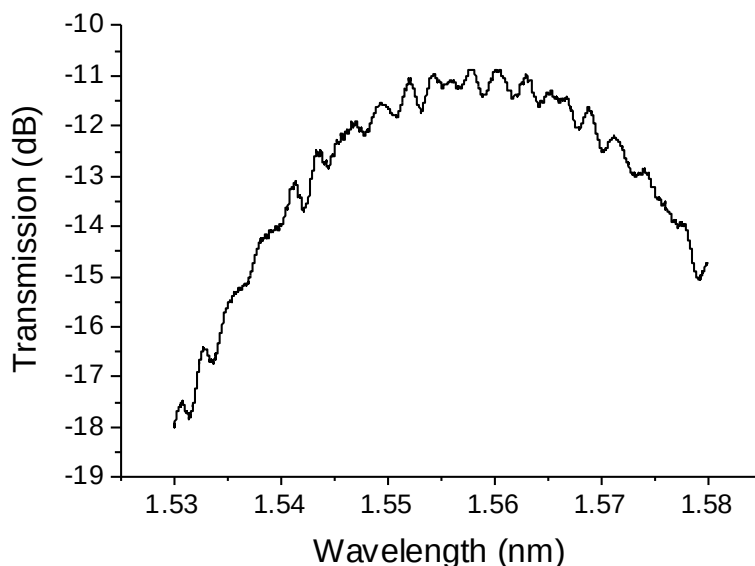
SOI500nm_1550nm_TE_RIB_Grating_Coupler

Platform:	500 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	160 nm (Grating etch depth)
Polarization:	TE
Cell name in GDS lib:	SOI500nm_1550nm_TE_RIB_Grating_Coupler

Dimensions:



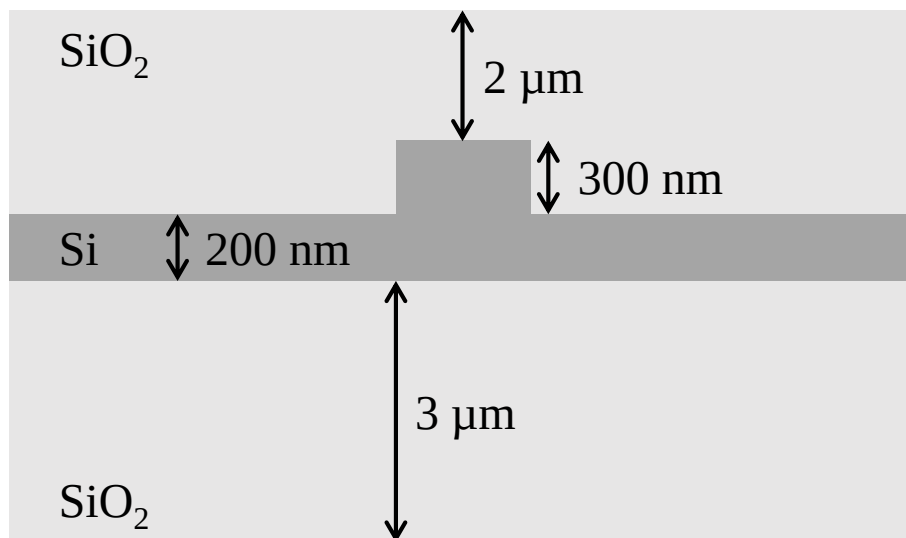
Measured transmission spectrum



Summarized performance:

- Coupling efficiency: 5-6 dB
- 1 dB bandwidth: > 30 nm
- Center wavelength: 1550-1570 nm

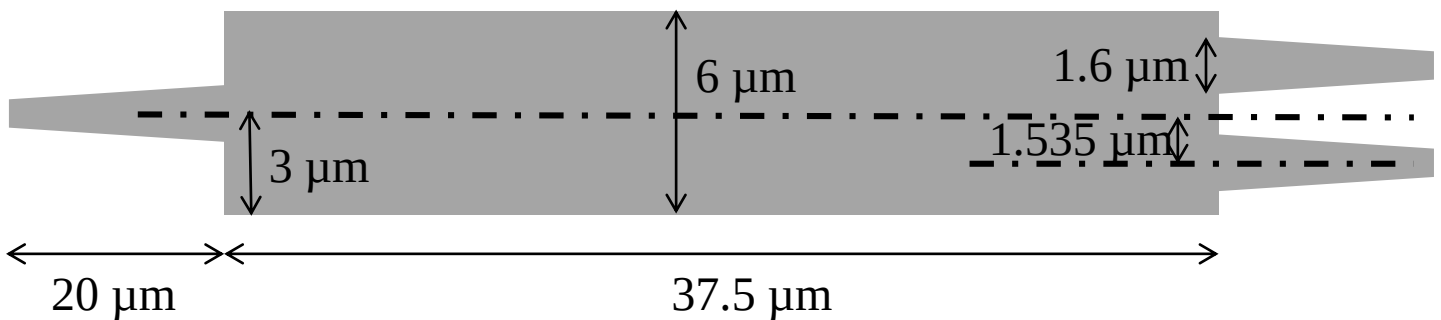
- Wavelength: 1550 nm
- Platform: 500 nm SOI
- **RIB**



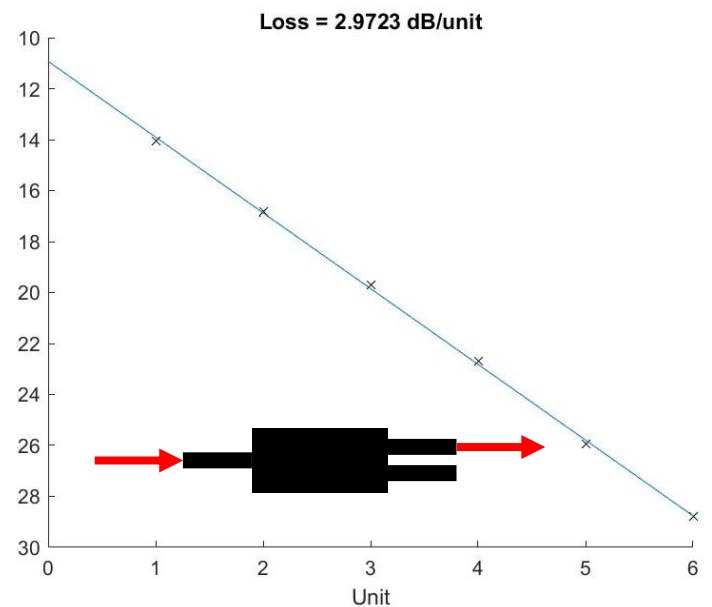
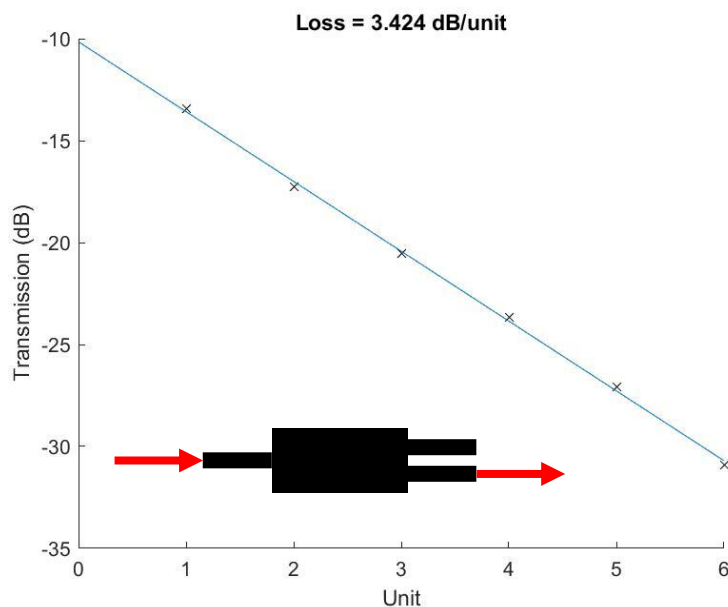
SOI500nm_1550nm_TE_RIB_2x1_MMI

Platform:	220 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	300 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI500nm_1550nm_TE_RIB_2x1_MMI

Dimensions:



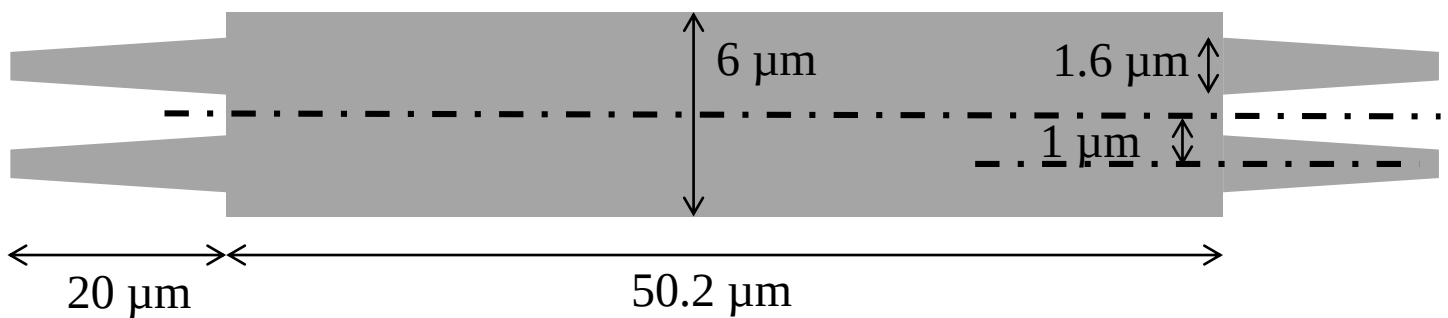
Measurement results:



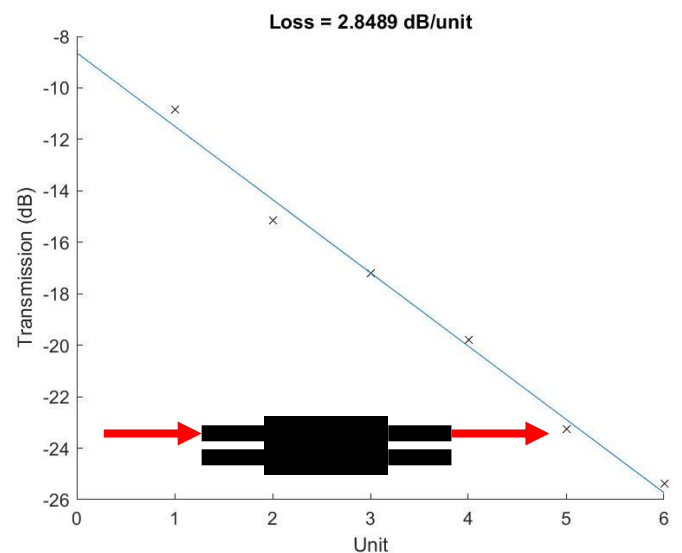
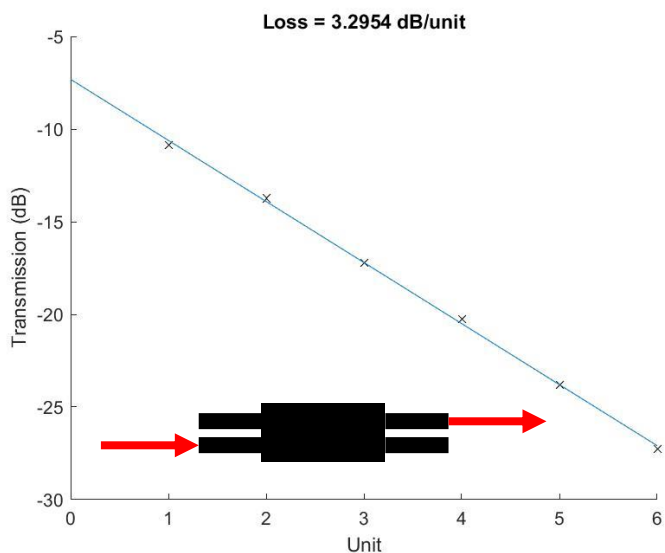
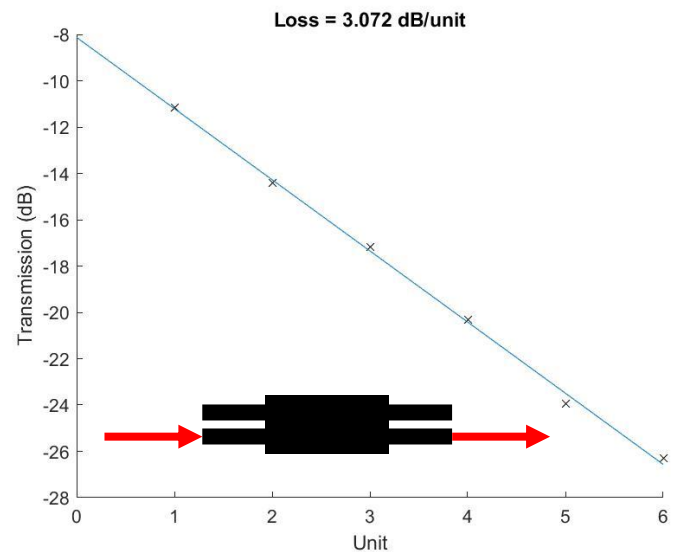
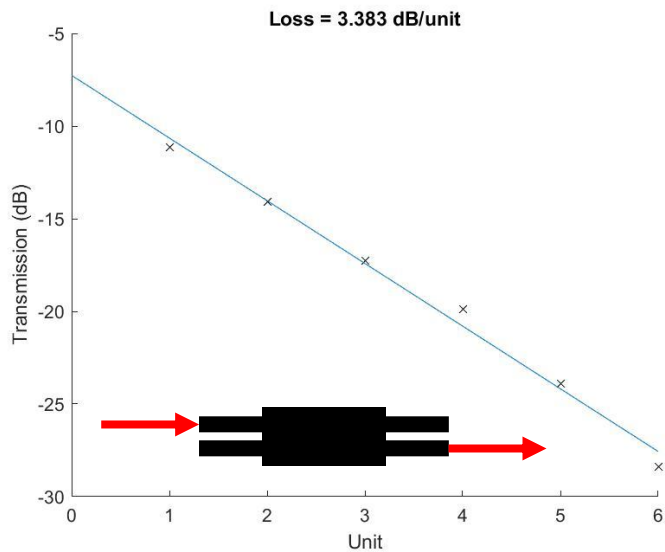
SOI500nm_1550nm_TE_RIB_2x2_MMI

Platform:	500 nm SOI (2 μm BOX layer)
Wavelength:	1550 nm
Etching depth:	300 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI500nm_1550nm_TE_RIB_2x2_MMI

Dimensions:



Measurement results:

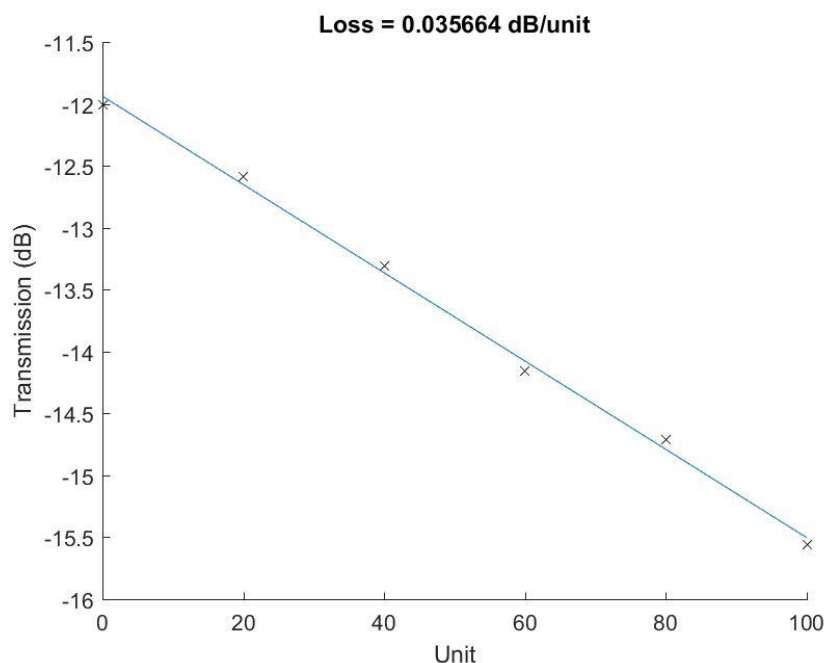


SOI500nm_1550nm_TE_RIB_90_Degree_Bend

Platform:	500 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	300 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI500nm_1550nm_TE_RIB_90_Degree_Bend (Waveguide Width (W): 450 nm, Bend Radius (R): 25 um)

Measurement results:

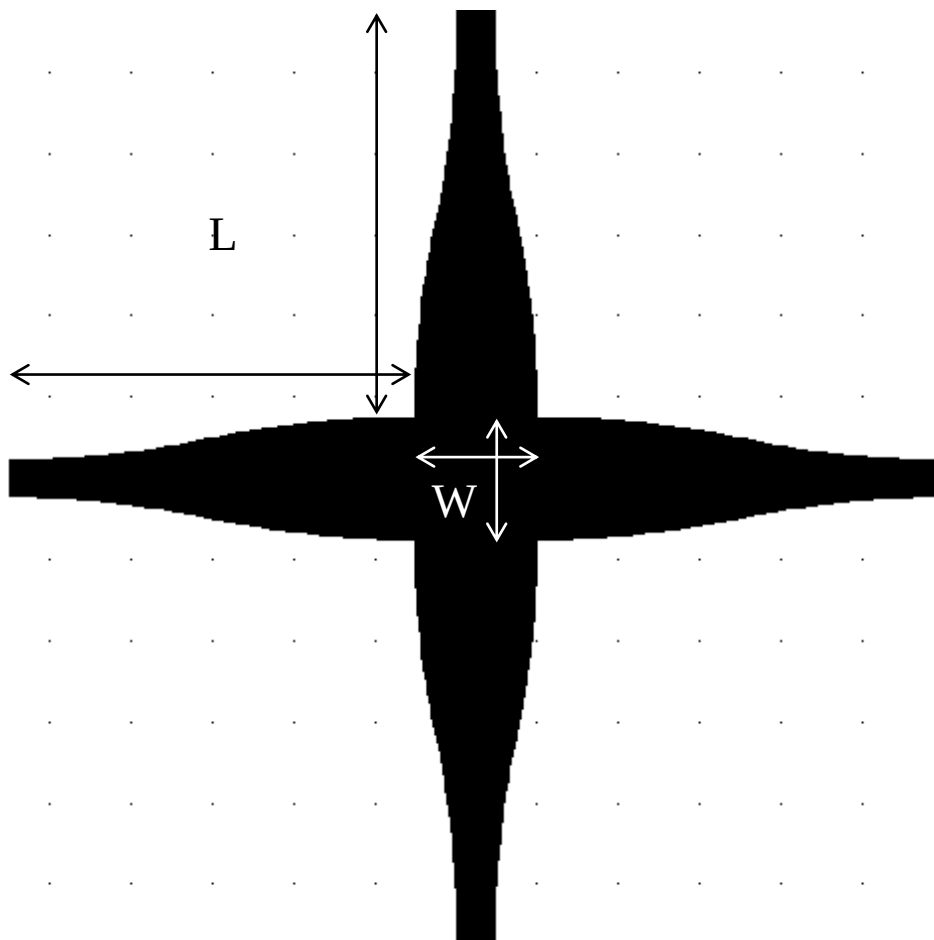
(Unit: 90° bend)



SOI500nm_1550nm_TE_RIB_Waveguide_Crossing_Curved Design

Platform:	500 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	300 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	Not in GDS library

Dimensions:



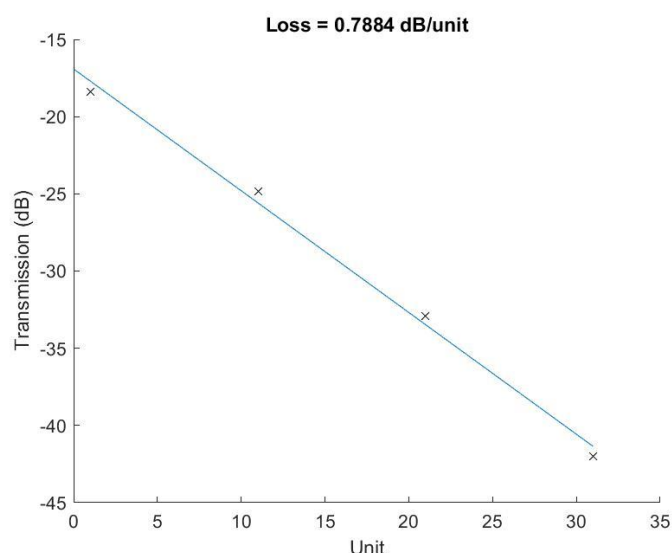
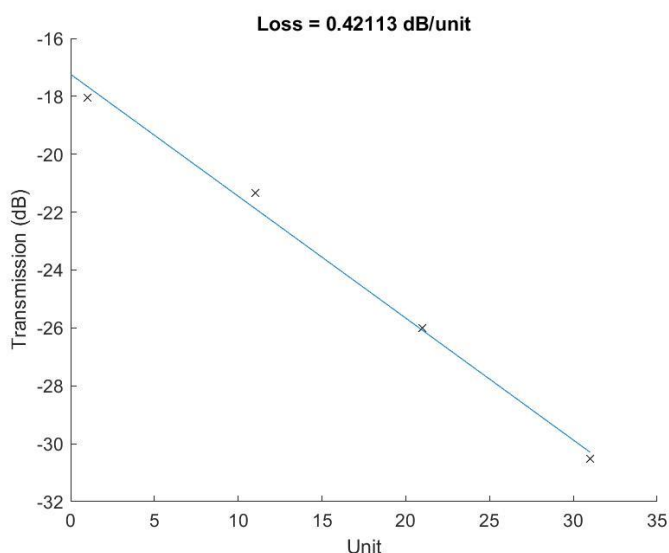
Measurement results on different dimensions: See next page

Measurement results on different dimensions (wavelength 1595-1605 nm):

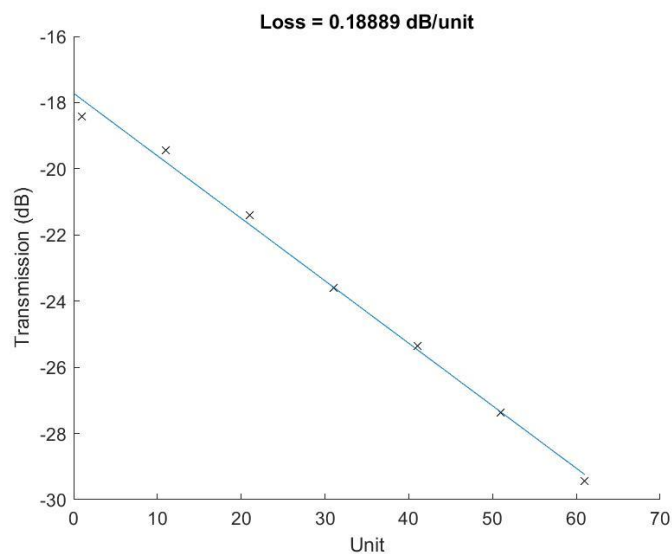
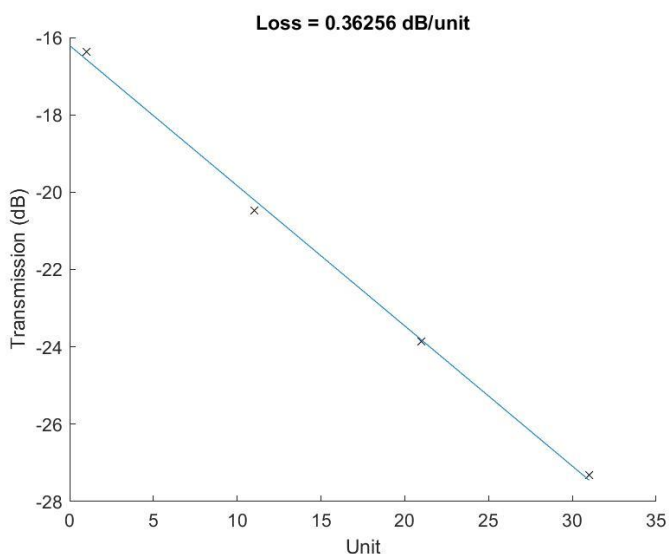
W: 1.2 μm

W: 1.5 μm

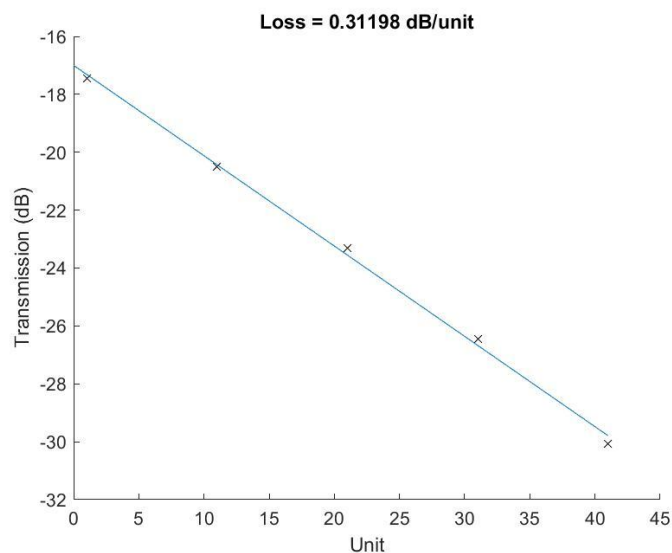
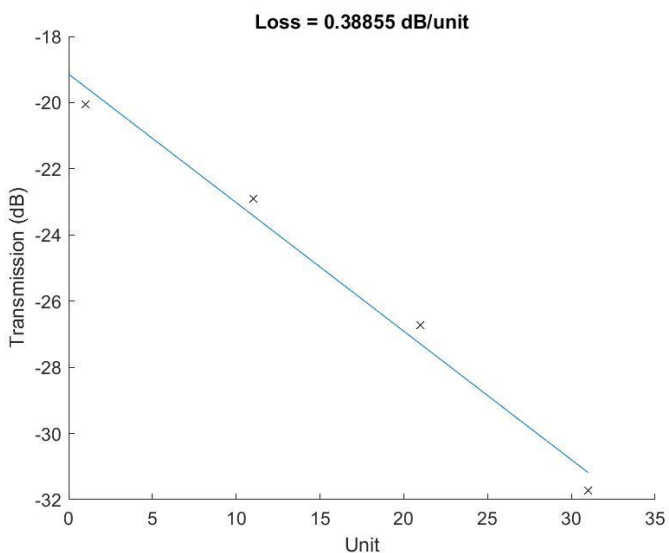
L: 5 μm



L: 8 μm



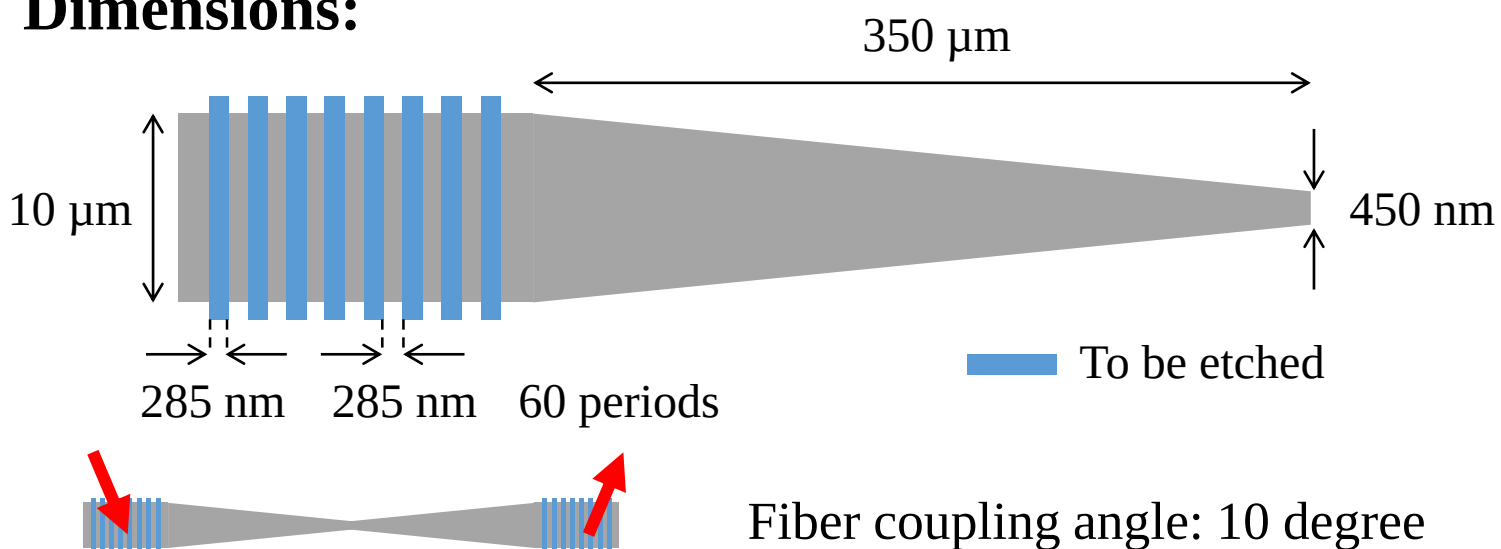
L: 10 μm



SOI500nm_1550nm_TM_RIB_Grating_Coupler

Platform:	500 nm SOI (2 μ m BOX layer)
Wavelength:	1550 nm
Etching depth:	160 nm (Grating etch depth)
Polarization:	TM
Cell name in GDS lib:	SOI500nm_1550nm_TM_RIB_Grating_Coupler

Dimensions:



Measured transmission spectrum

Summarized performance:

- Coupling efficiency:
dB
- 1 dB bandwidth:
> nm
- Center wavelength:
nm